DANAE - a new experiment for direct dark matter detection with DEPFET silicon detector

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ÖAW

25 June 2018
DSU 2018
Annecy-le-vieux

DANAE (DANAË)

Direct dArk matter search using DEPFET with repetitive-Non-destructive-readout Application Experiment

OeAW funding for detector technology

“Danae” by G. Klimt

Collaboration

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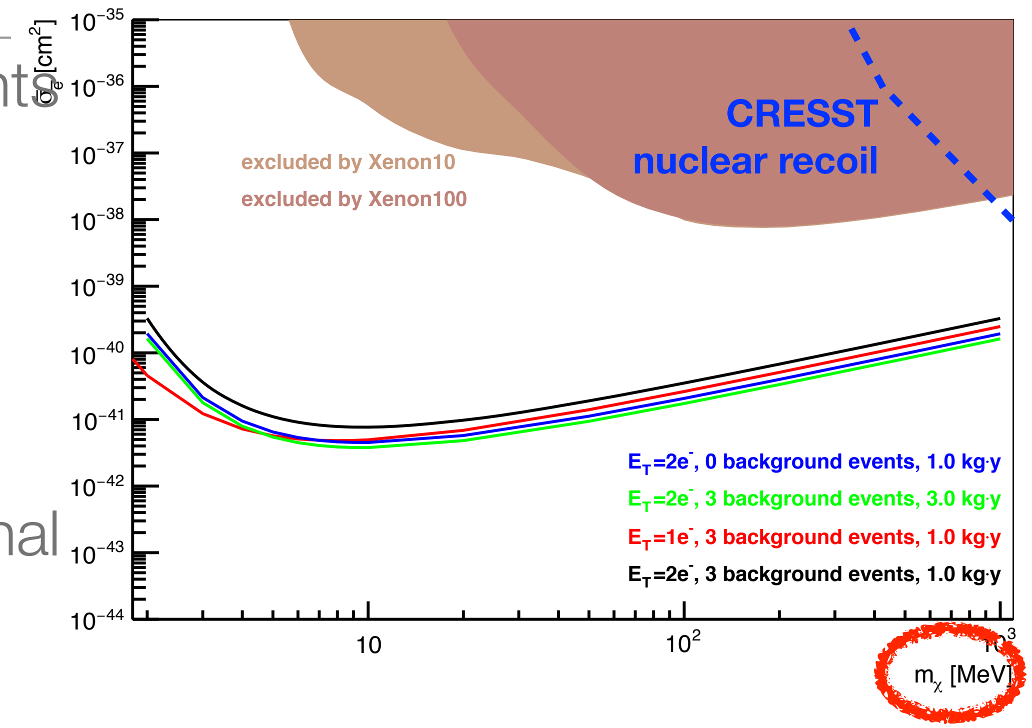
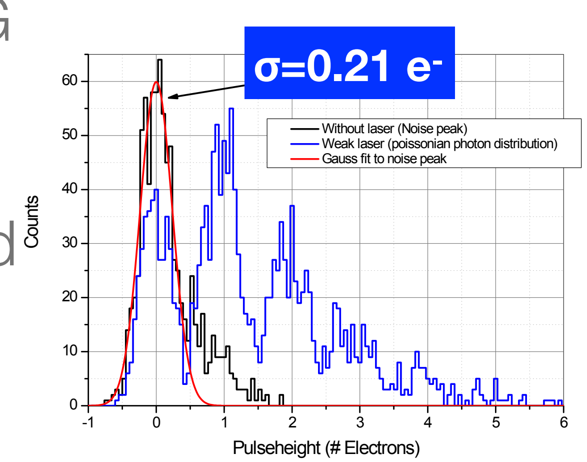
Atominstitut, Technische Universität Wien, Vienna, Austria [C]

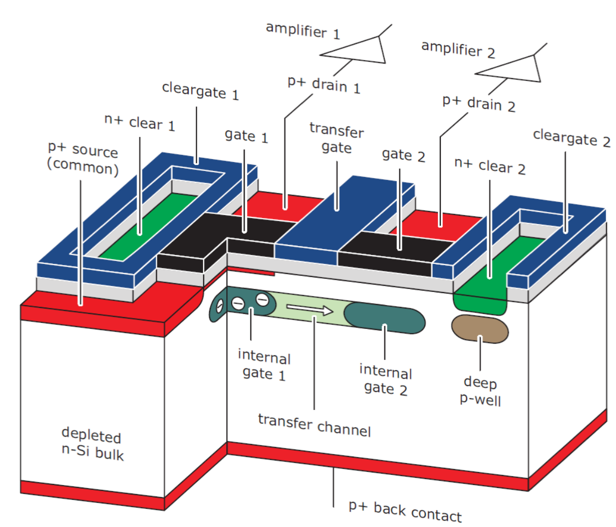
The project overview

Direct Dark Matter Detection with DEPFET

- minimal reach for nuclear recoil experiments about few 100 MeV
- dark matter electron scattering offers **reach towards MeV dark matter**
- measurement of **low noise** ionisation signal in **low background** environment
- RNDR* DEPFET sensors developed by semiconductor laboratory of MPG
- setup for **proof-of-principle measurement** currently prepared
- expect first results early 2019







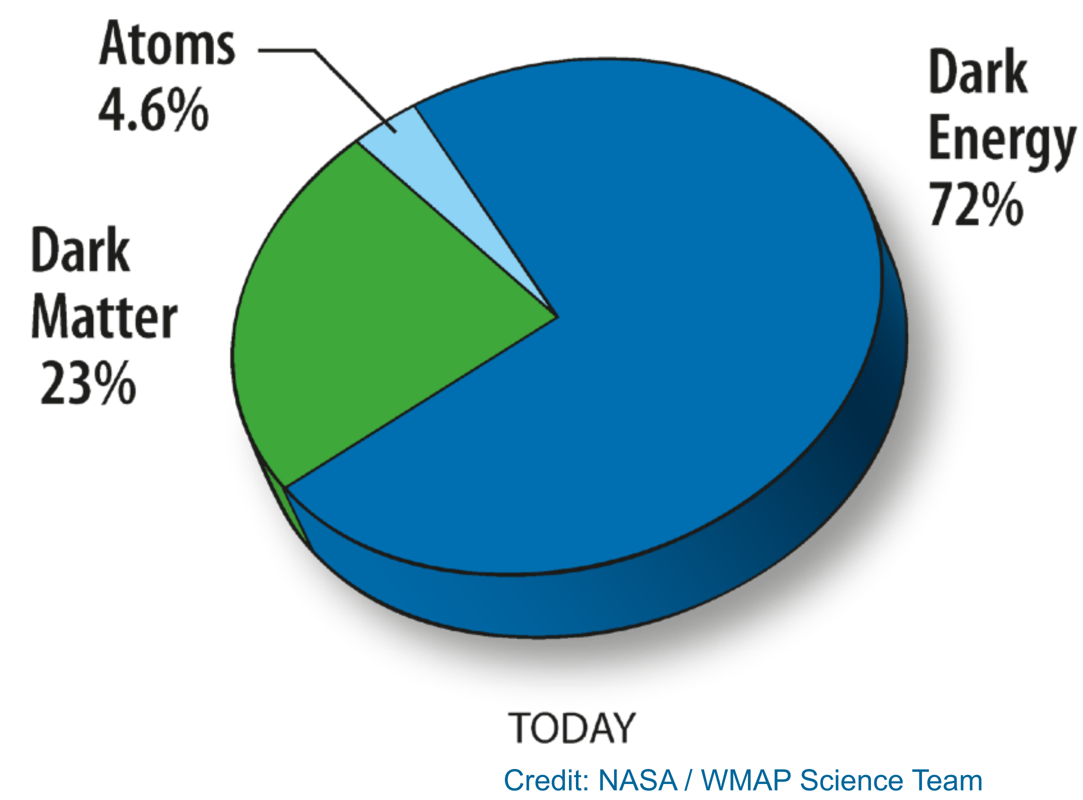
EPJ C, 77(12), 279 (2017)

*Repetitive Non-Destructive Readout

from Jochen Schieck "Experimental Dark Matter Search at HEPHY"

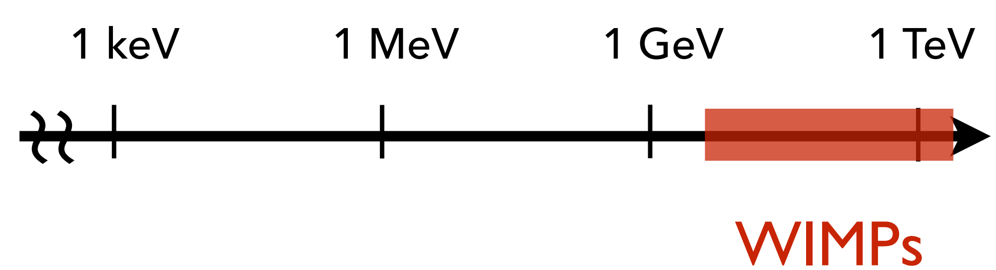
Dark matter landscape - partly

Over 80% of the mass in the universe is invisible dark matter



"WIMP" as a dark matter candidate :

- weakly interacting with matter
  $<\sigma_{WIMP} \cdot v> \sim G_F^2 \cdot m_X^2 \sim 1/\Omega_X$
- fits the Hubble constant and "relic" density of dark matter



predicts dark matter WIMP mass between 2 GeV and 120 TeV

dominated the direct detection experiments until recently

WIMP direct detection method

look for nuclear recoils from WIMP-nucleus scattering

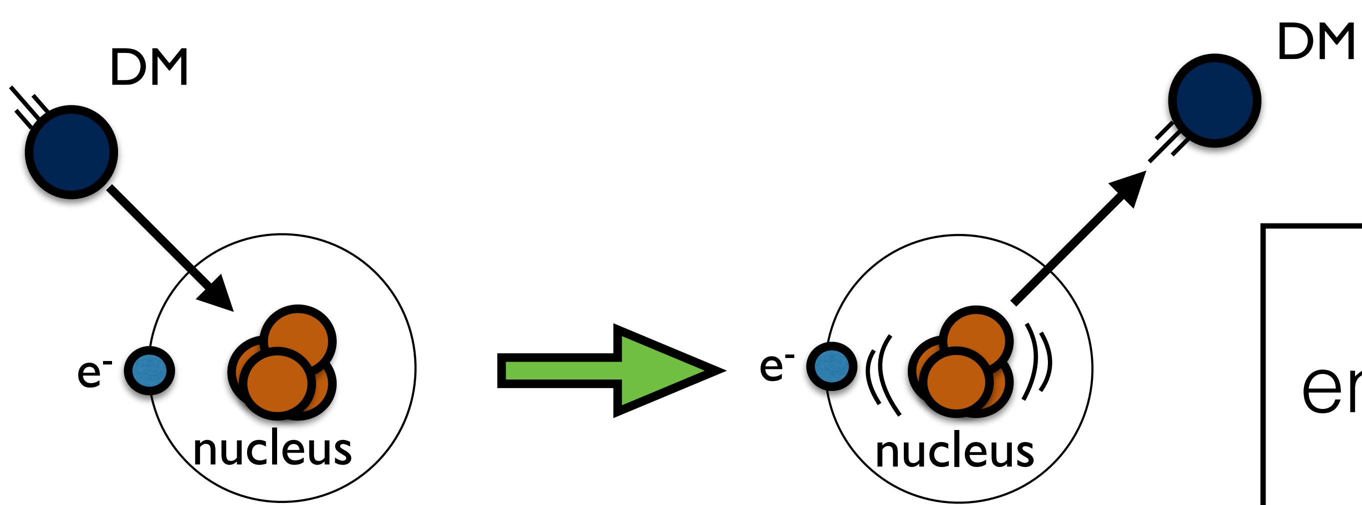


image credit R. Essig

Energy deposit in target material in forms of :
- light
- phonon
- electric charge

Detection limitation :
energy deposit from nucleus recoil
$E_{NR} \sim 2\mu_{\chi,N}{}^2 . v_\chi / m_N$

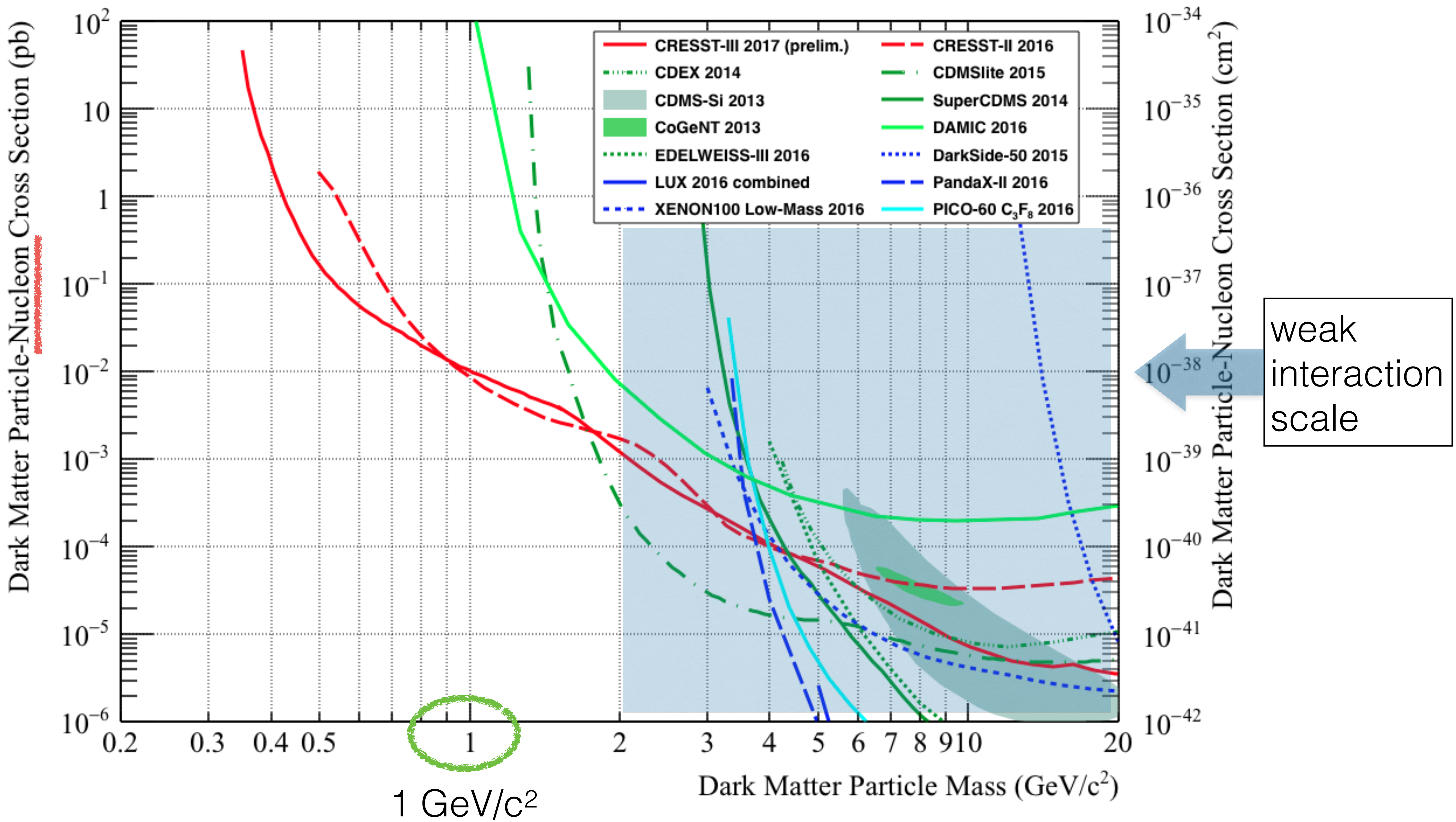
-> for 100 MeV m_χ, $E_{NR} \sim 1$ eV *

plus quenching factors and noise level of the detectors

typical DM velocity $v_\chi \lesssim 800~\mathrm{km/s}$

*for silicon

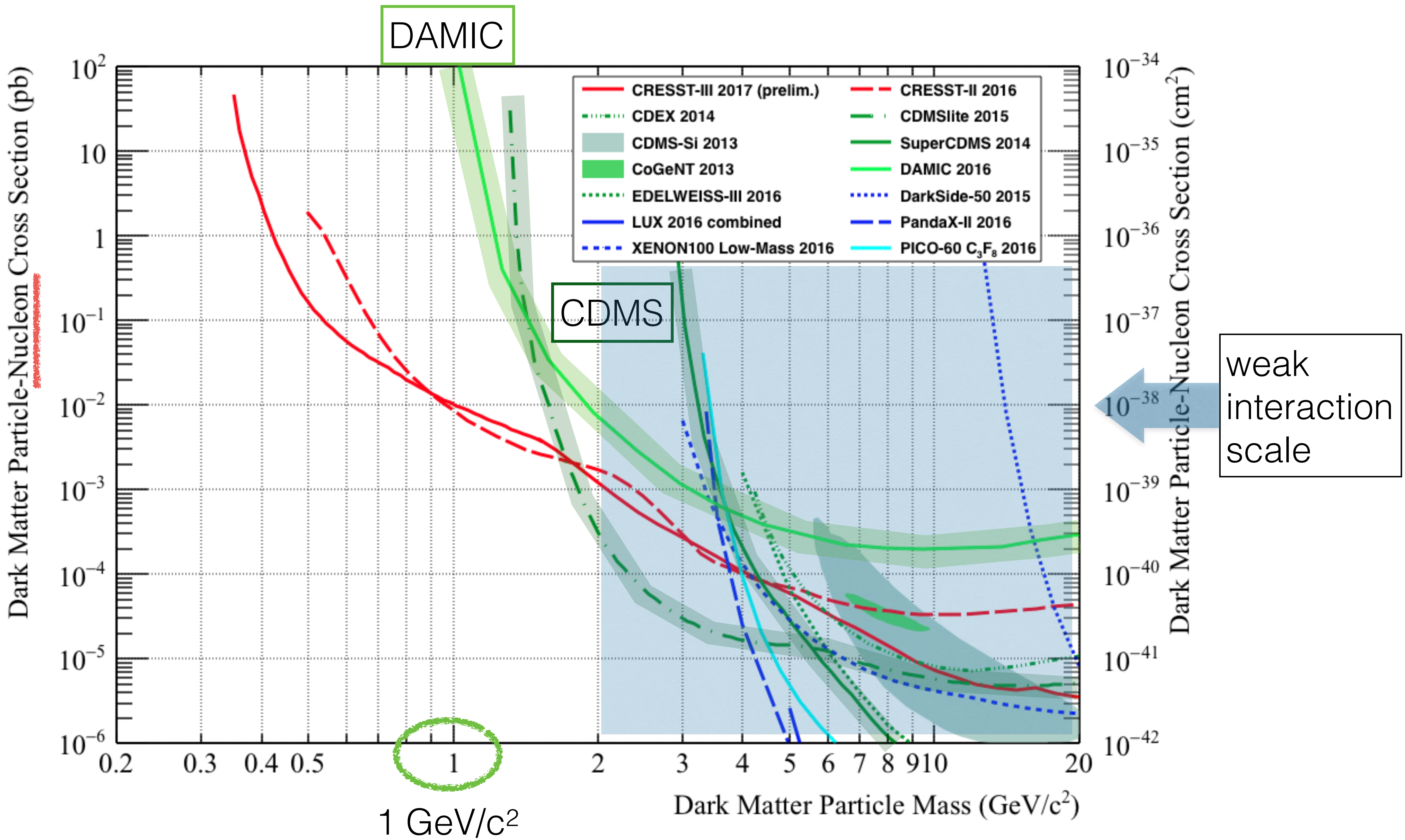
DM-nucleus scattering direct search status



no evidence for WIMP yet

arXiv:1711.07692

DM-nucleus scattering direct search status



no evidence for WIMP yet

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Dark Sector and Light Dark Matter

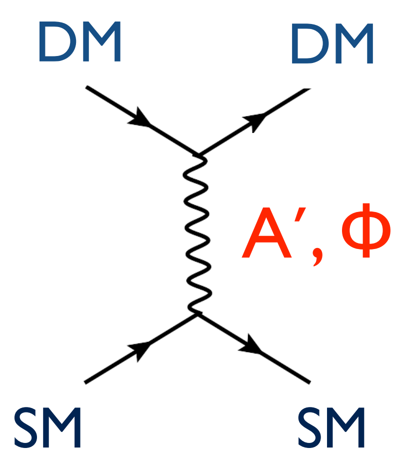
Dark sectors

(DM + new mediators)

WIMPs

several sharp "theory" targets

(freeze-out, asymmetric, freeze-in, SIMP, ELDER)



DM scattering

image credit R. Essig

Dark sector :

interaction between DM and standard model particle mediated by a dark photon

(one example of mediators)

clear predictions from multiple models over wide DM mass region, including keV ~ GeV range

-> comparable observables in experiments

DM-electron scattering

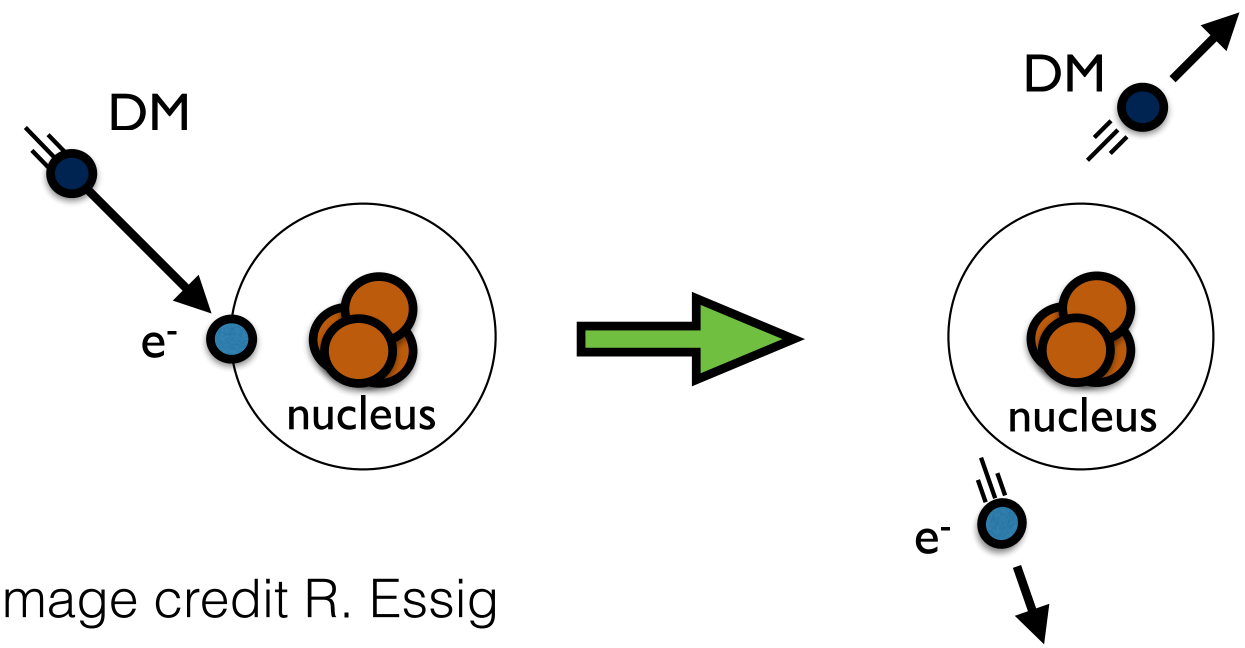


image credit R. Essig

kinematically

to overcome binding energy ΔE

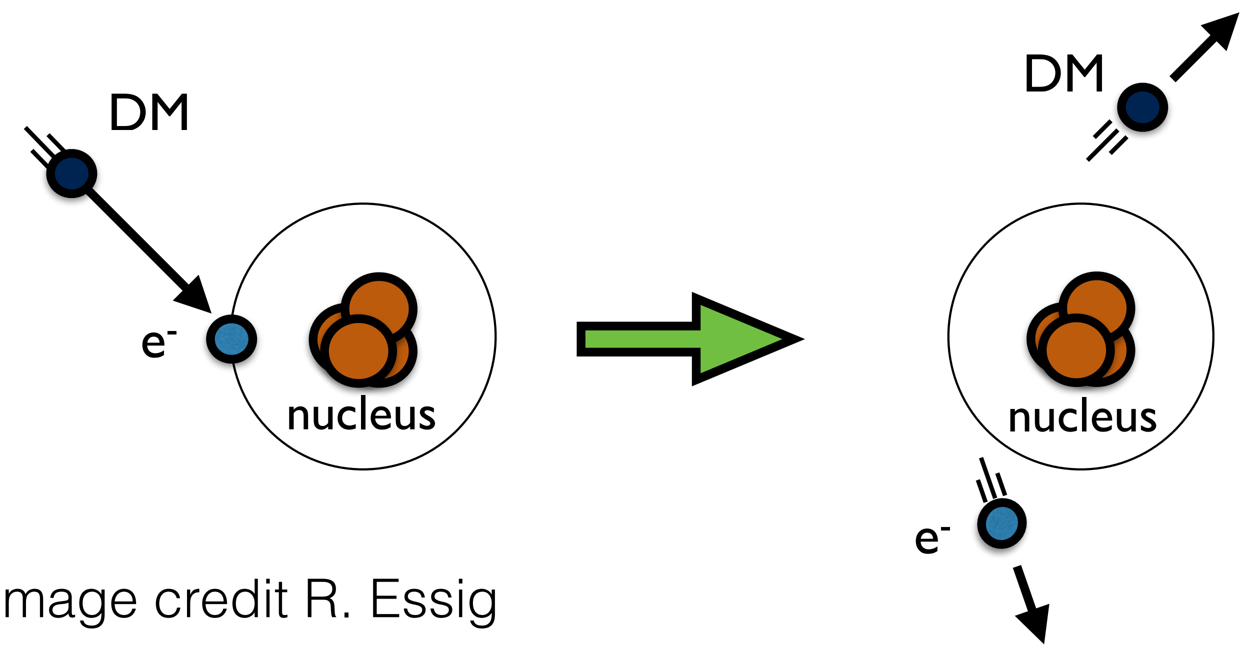
need $E_{\rm DM} \sim \frac{1}{2} m_{\rm DM}\, v_{\rm DM}^2 > \Delta E$

$$v_{\rm DM} \lesssim 800 \text{ km/s} \implies \boxed{m_{\rm DM} \gtrsim 300 \text{ keV} \left(\frac{\Delta E}{1 \text{ eV}}\right)}$$

O(100 keV)

JHEP05(2016)046

DM-electron scattering



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kinematically
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$v_{\rm DM} \lesssim 800~{\rm km/s} \Longrightarrow \boxed{m_{\rm DM} \gtrsim 300~{\rm keV} \left(\frac{\Delta E}{1~{\rm eV}}\right)}$

O(100 keV)

bound e- does not have definite momentum,
typical momentum transfer is set by e- not by DM.

$q_{\rm typ} \sim \alpha m_e \sim 4~{\rm keV}$ (for outer shell electron)

transferred energy: $\Delta E_e \sim \vec{q} \cdot \vec{v}_{\rm DM}$

$$\boxed{\Delta E_e \sim 4~{\rm eV}}$$

typical
recoil energy

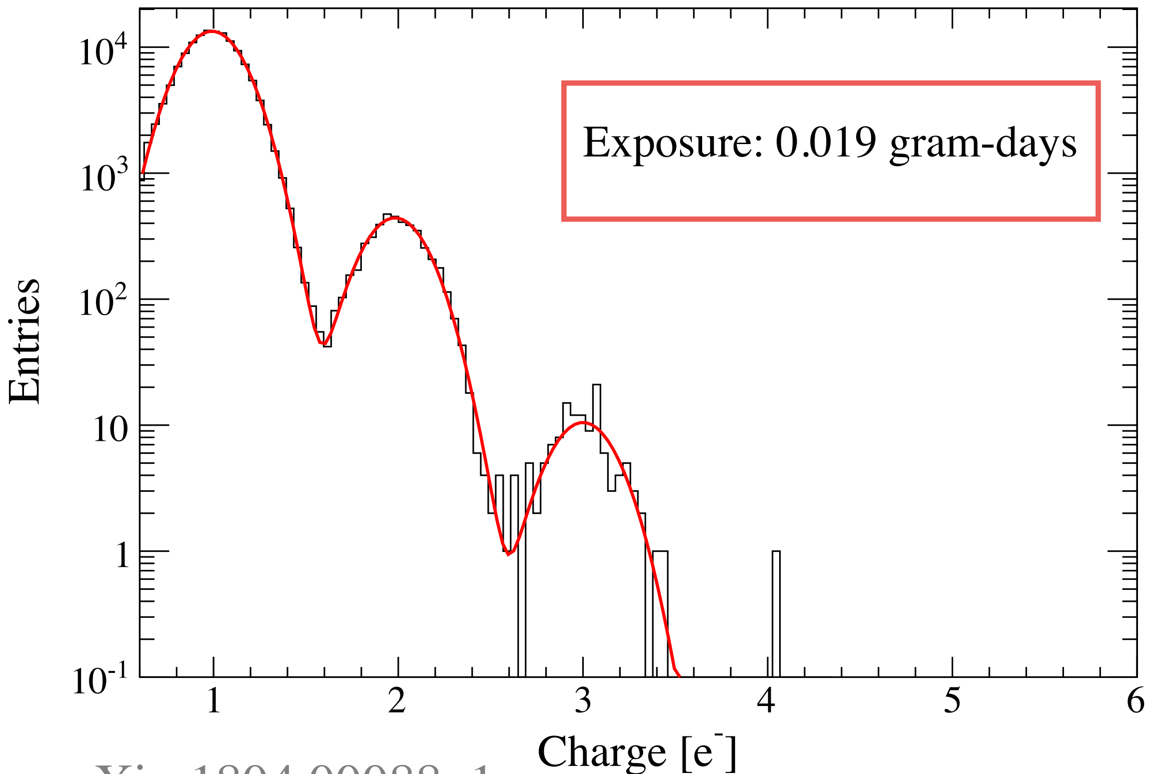
JHEP05(2016)046

Target materials for electron recoils

Target Type	Examples	E_{th}	m_χ threshold	Status	Timescale
Noble liquids	Xe, Ar, He	~ 10 eV	~ 5 MeV	Done w data; improvements possible	existing
Semi-conductors	Ge, **Si**	~ 1 eV	~ 200 keV	(E_{th} ~ 40 eV SuperCDMS, **DAMIC**) E_{th} ~ 1eV **SENSEI**, **DEPFET** R&D	~ 1-2 years
Scintillators	GaAs, NaI, CsI, …	~ 1 eV	~ 200 keV	R&D required	≲ 5 years
Supferfluid	He	~ 1 eV	~ 1 MeV	R&D required unknown background	≲ 5 years
Super-conductor	Al	~ 1 meV	~ 1 keV	R&D required unknown background	~ 10 - 15 years

arXiv:1608.08632

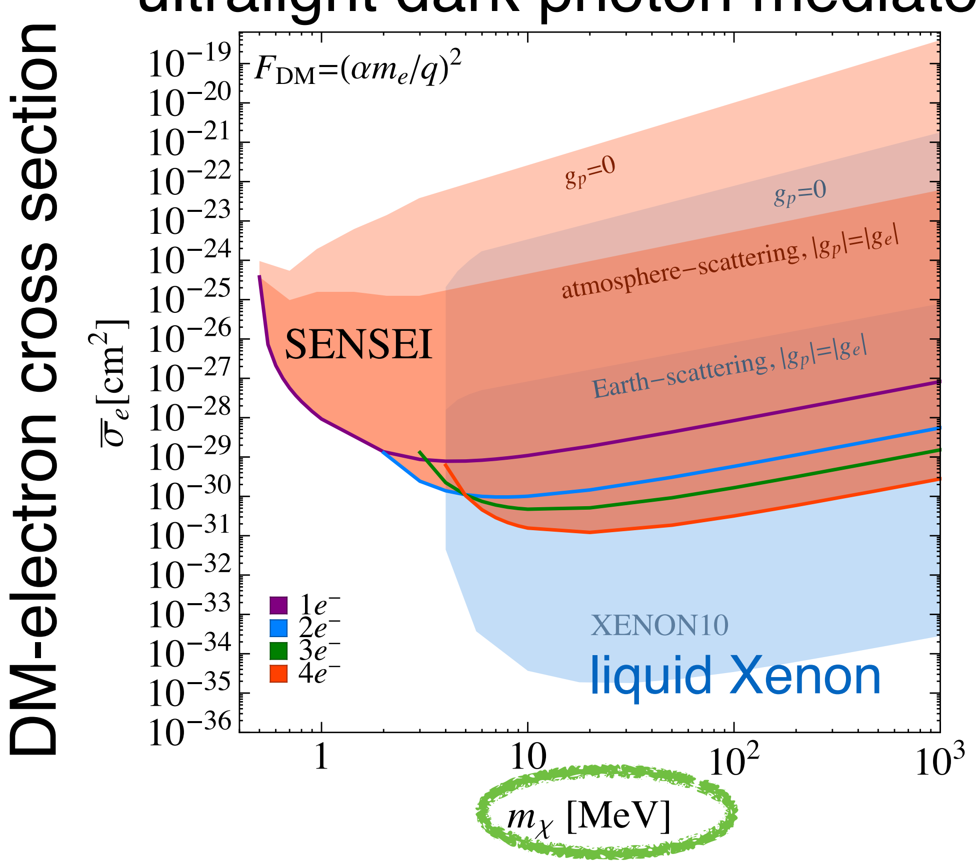
SENSEI first result with “skipper” CCD



arXiv:1804.00088v1

Active mass : 0.071 grams
427 minutes exposure (0.33 g-hr)
above sea level 220 m
single read noise : ~ 4 e-
<u>effective noise : ~ 0.14 e- (800 repetitions)</u>
<u>dark current : ~1.14 e-/pixel/day</u>
assume all events DM induced
-> conservative limit

ultralight dark photon mediator



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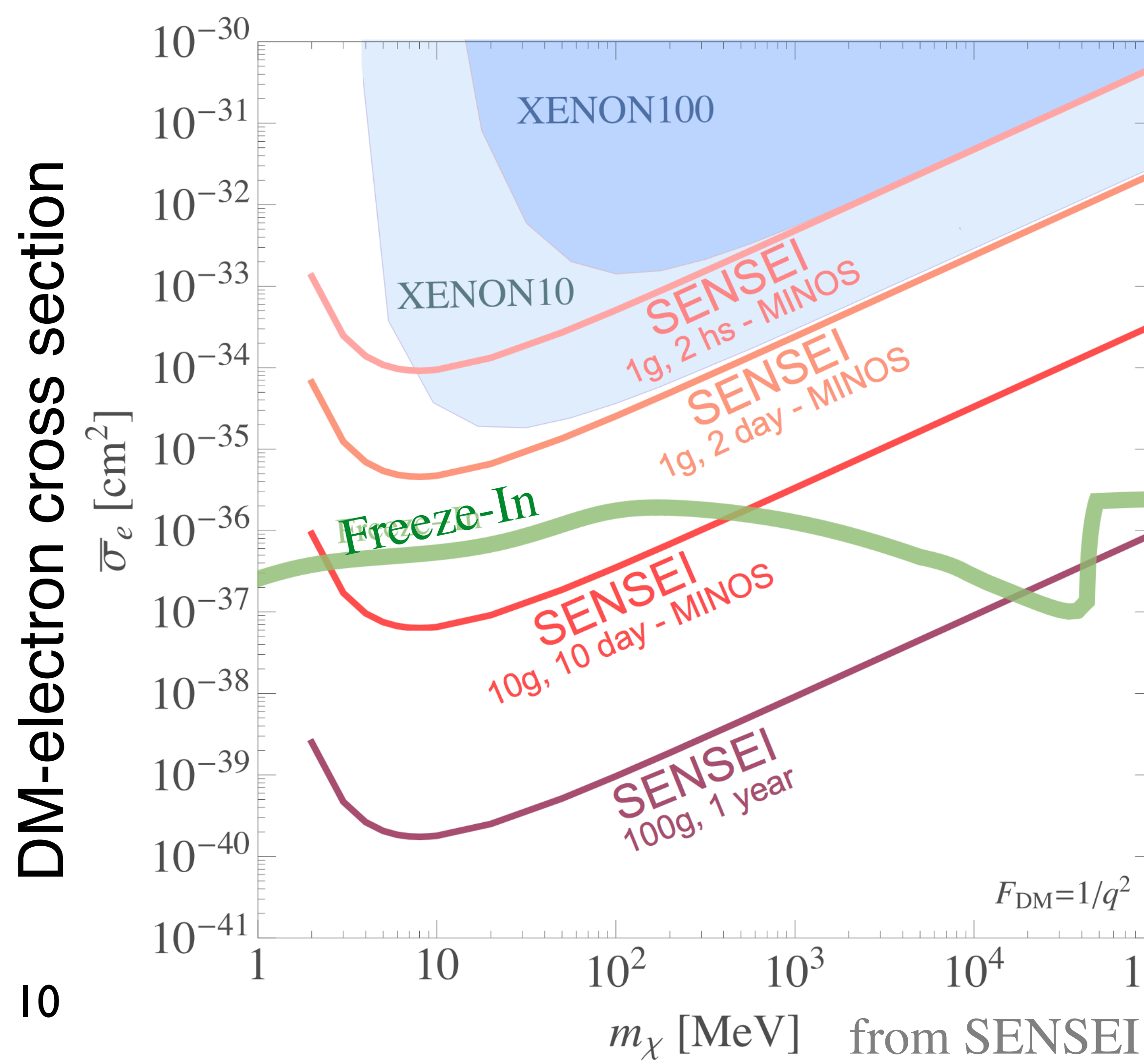

from SENSEI homepage

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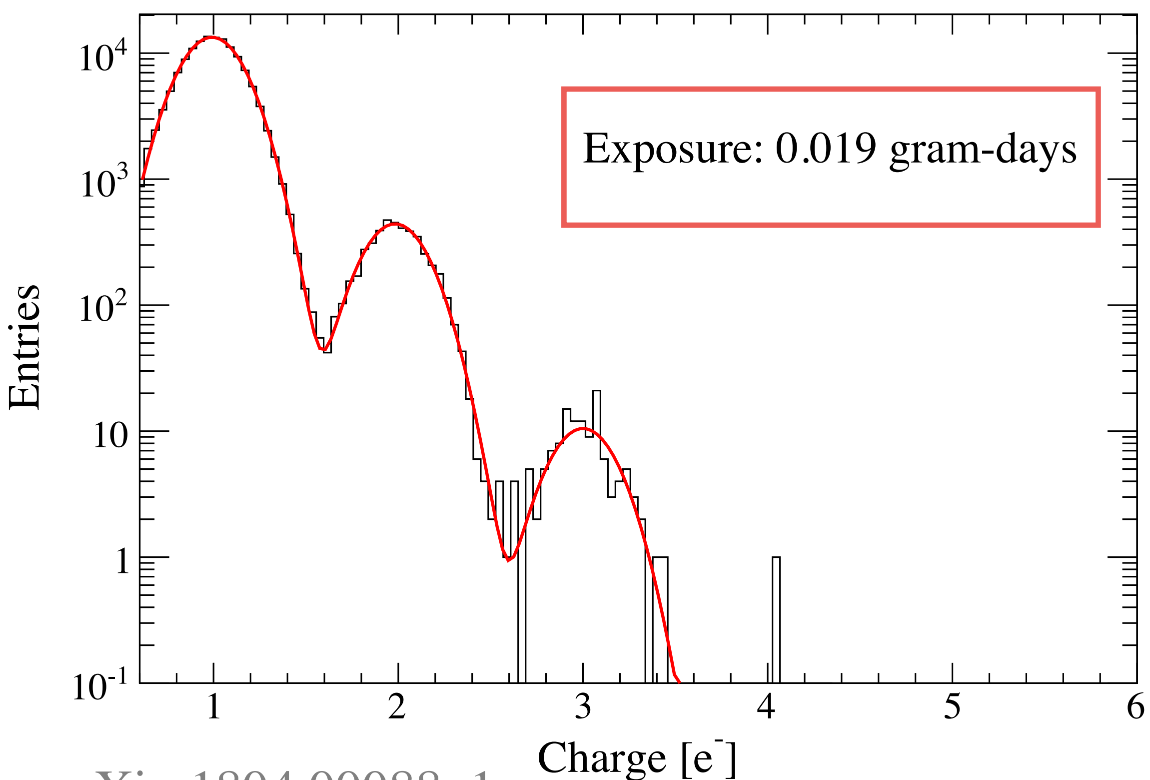

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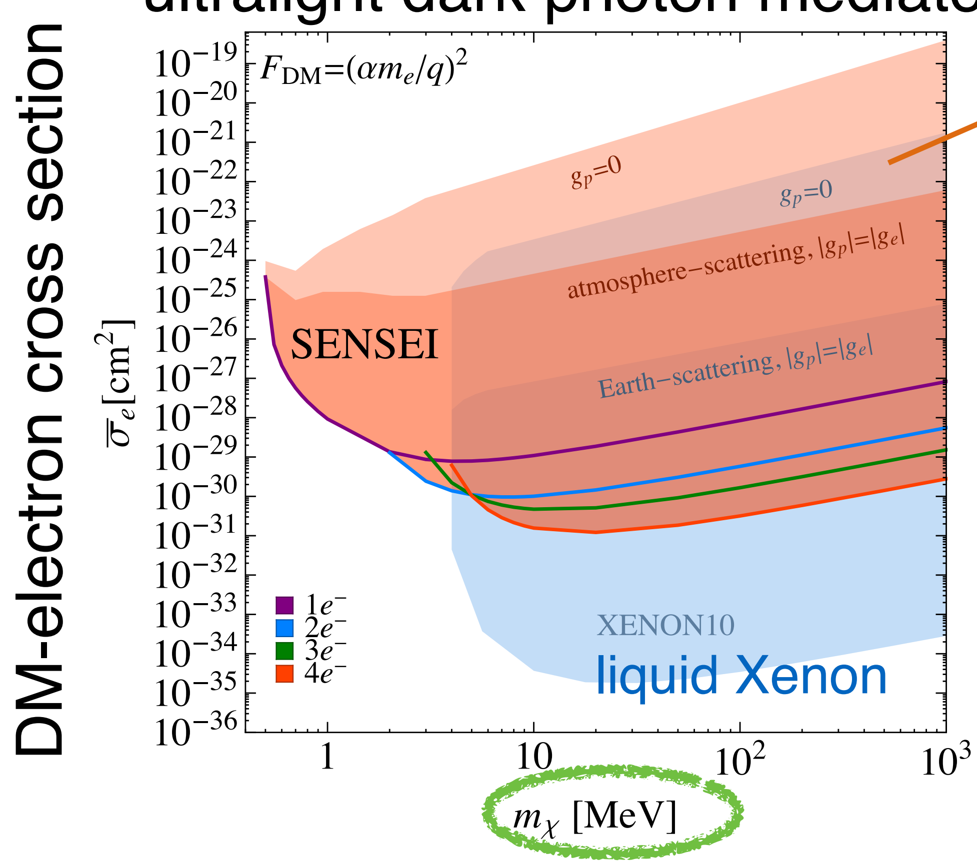

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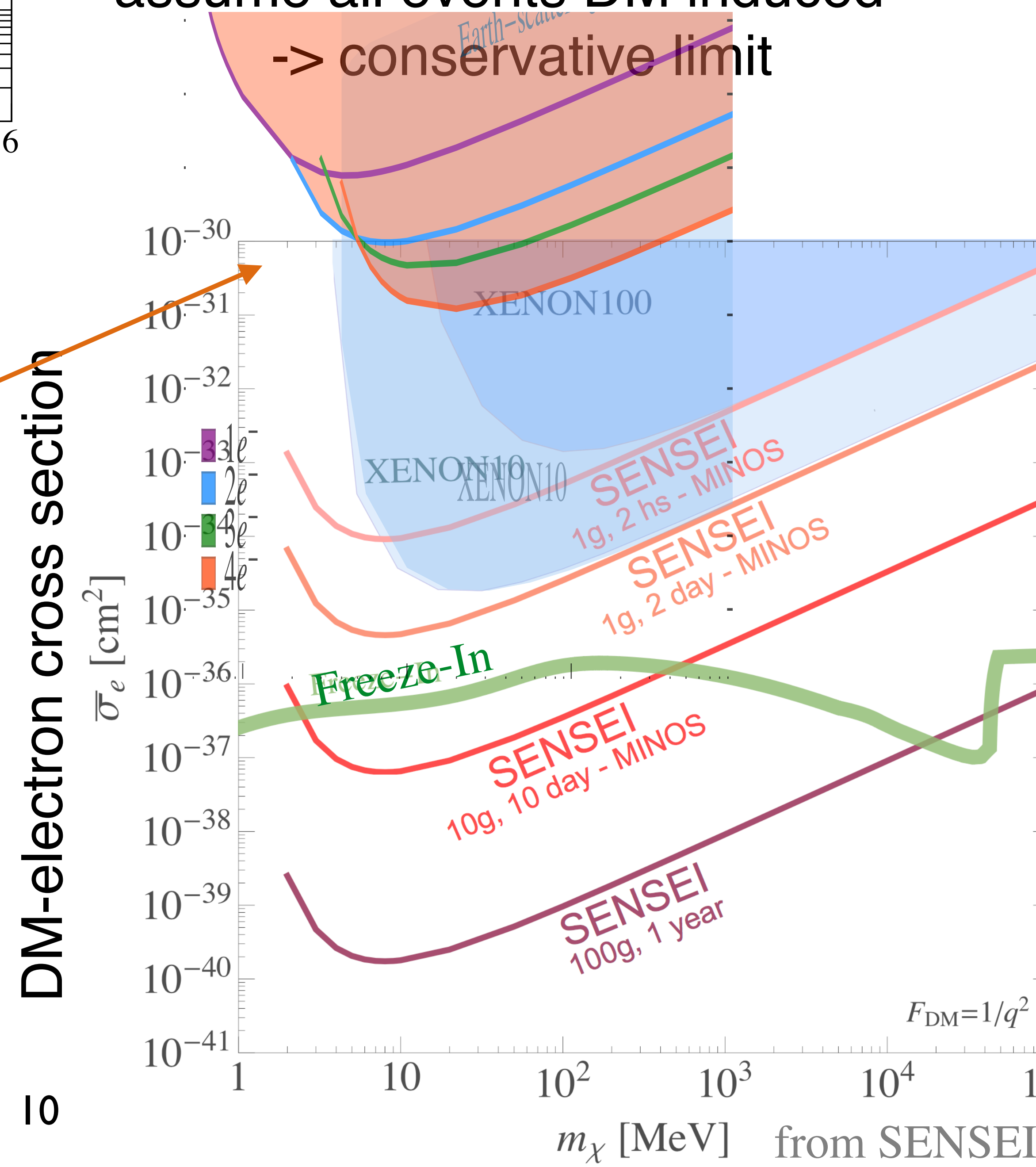


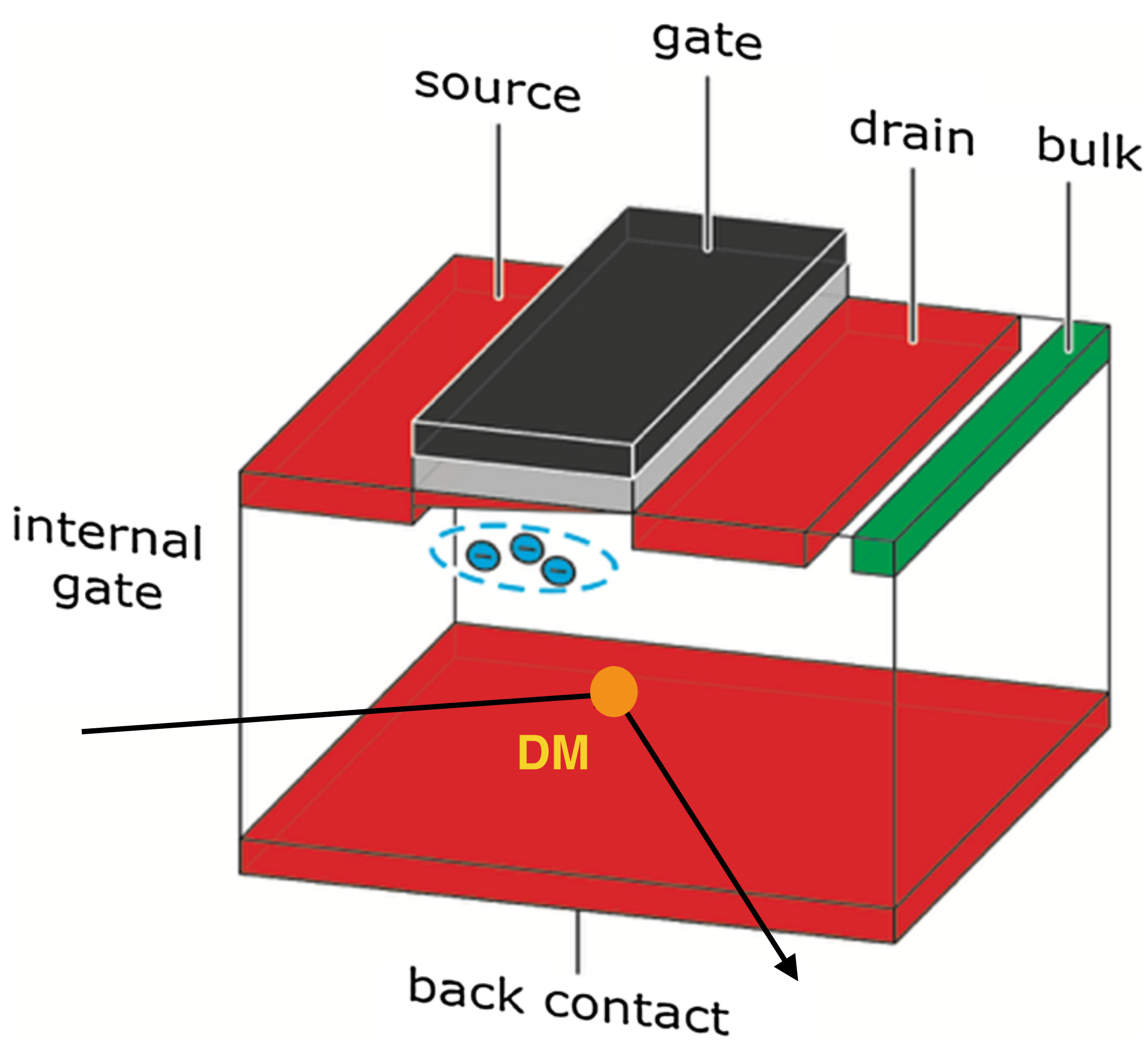
from SENSEI homepage

DEPFET with RNDR

RNDR : repetitive non-destructive readout

structure of a basic DEPFET cell :

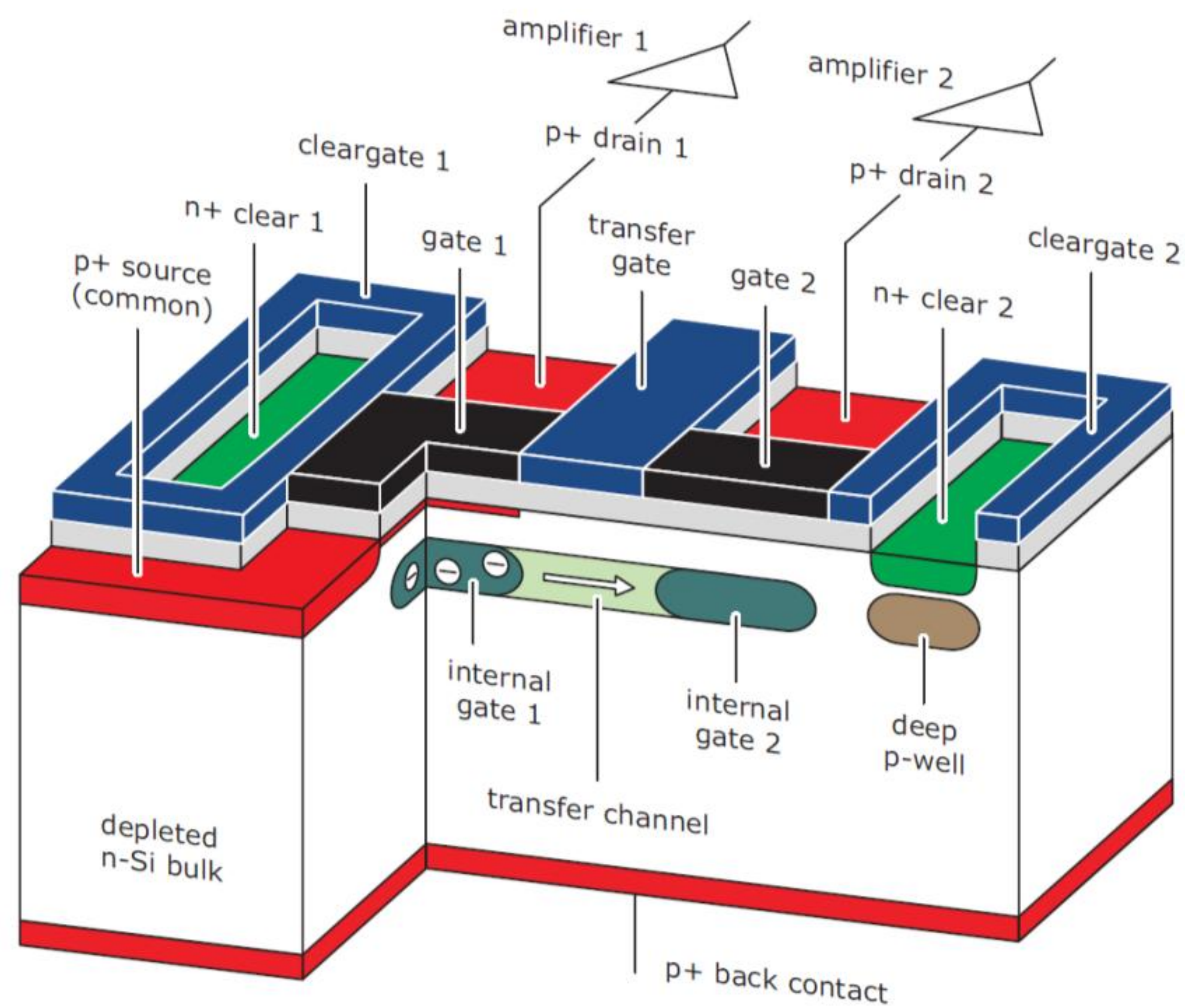
a “subpixel”



EPJ C, 77(12), 279 (2017)

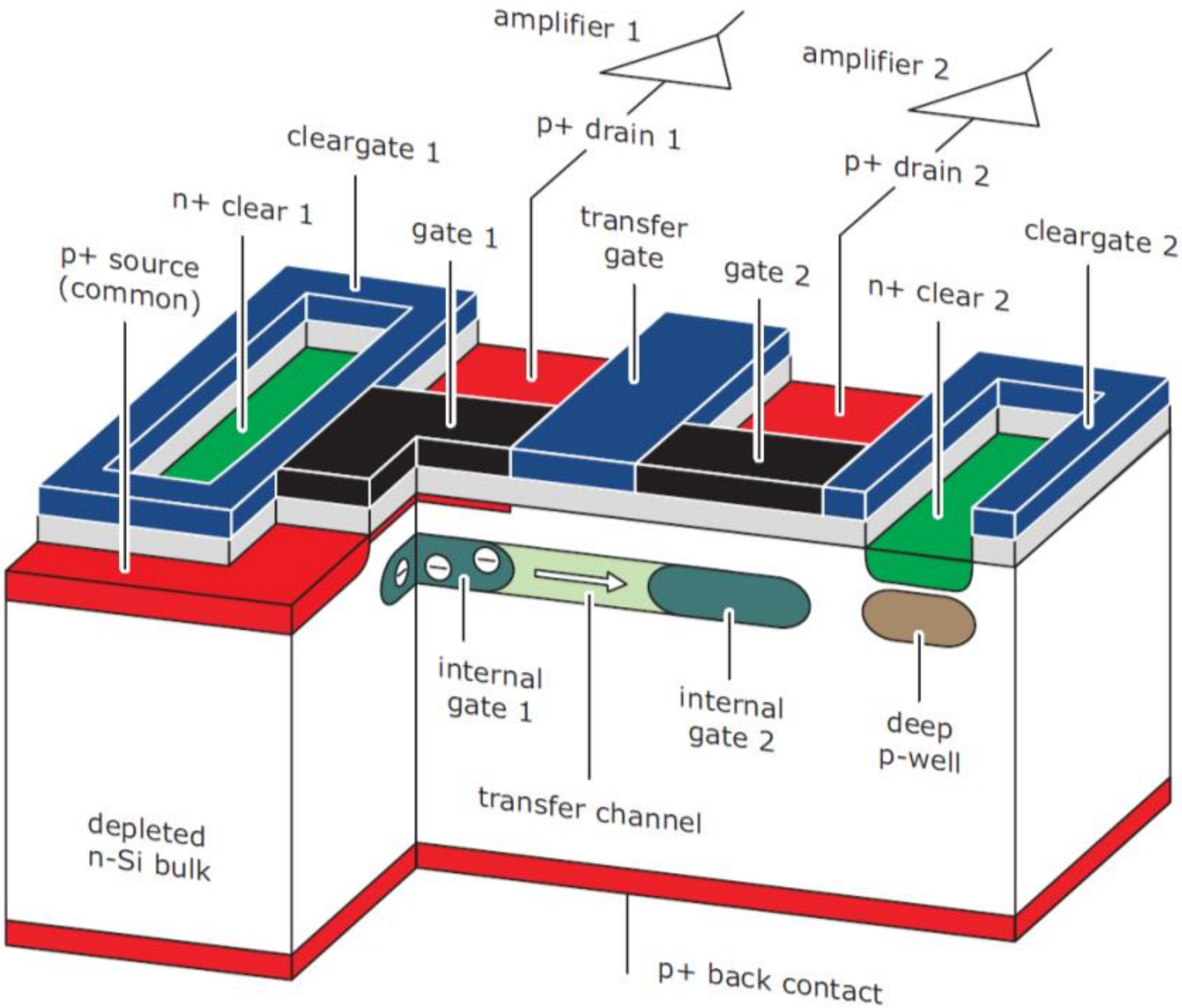
fully-depleted n-Si

structure of RNDR DEPFET “super-pixel”



EPJ C, 77(12), 279 (2017)

RNDR



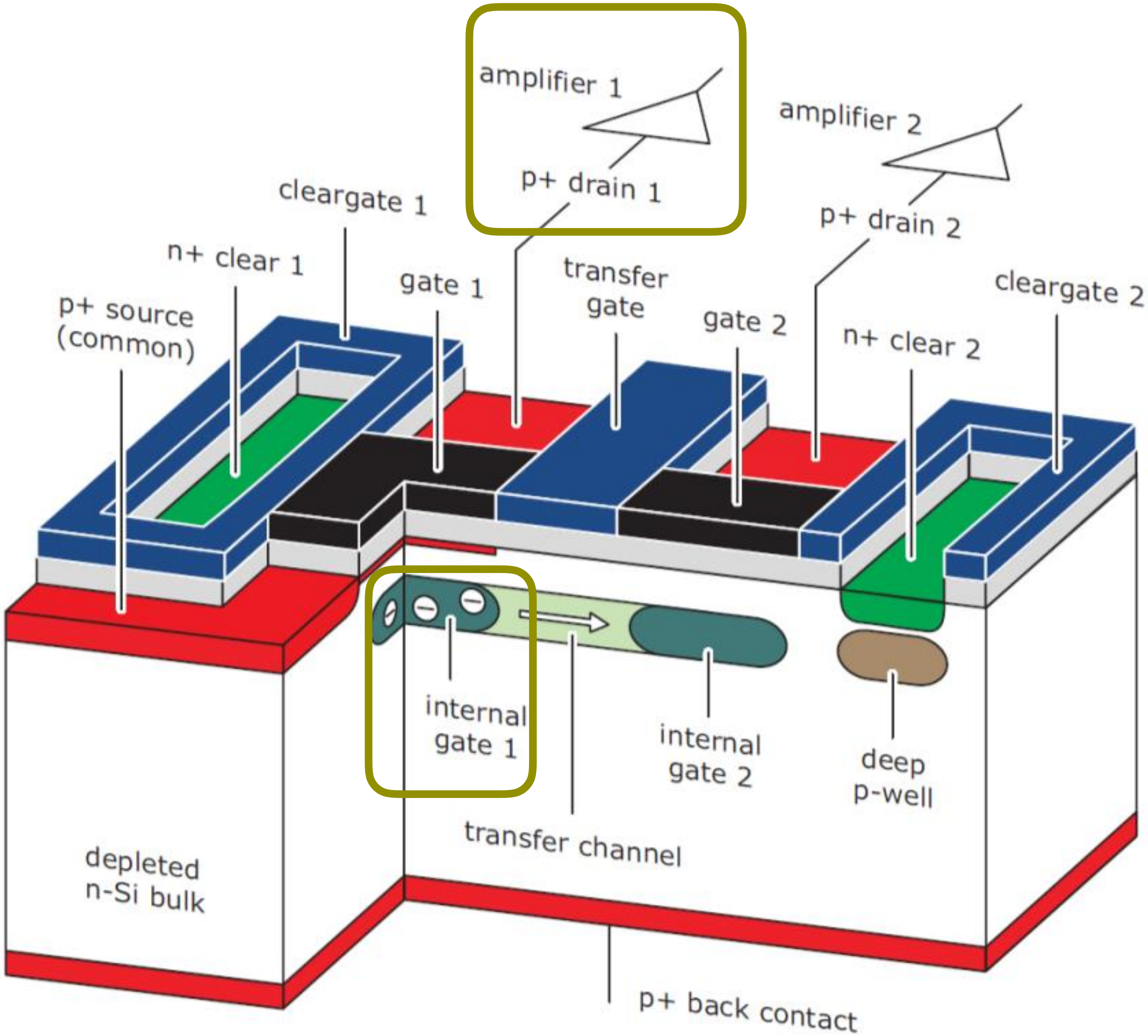
EPJ C, 77(12), 279 (2017)

RNDR readout

read N times *effective noise* :

$$\sigma_{eff} = \sigma/(\sqrt{N})$$

RNDR



EPJ C, 77(12), 279 (2017)

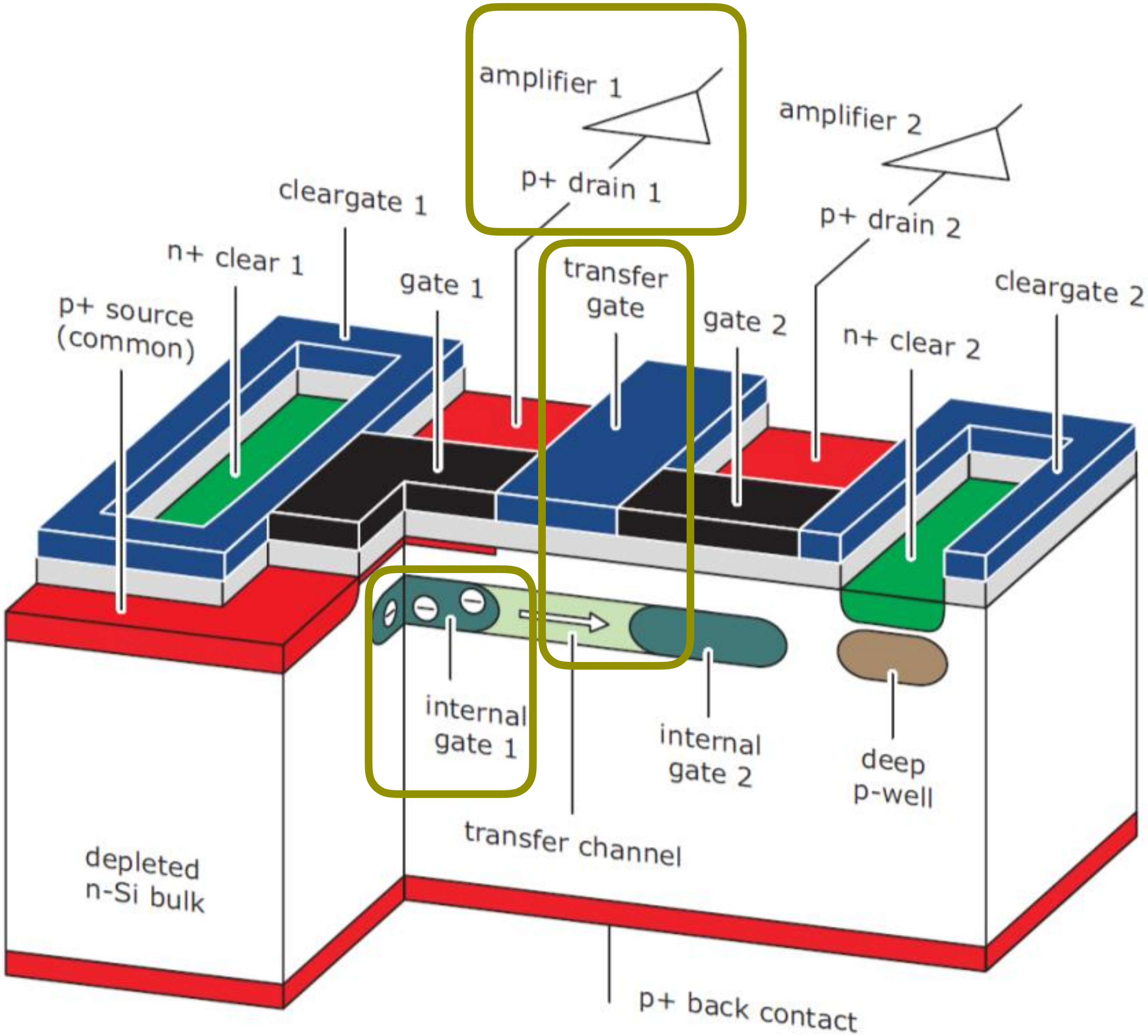
RNDR readout

read **1** : noise **σ**

read N times *effective noise* :

$$\boldsymbol{\sigma_{eff} = \sigma/(\sqrt{N})}$$

RNDR



EPJ C, 77(12), 279 (2017)

RNDR readout

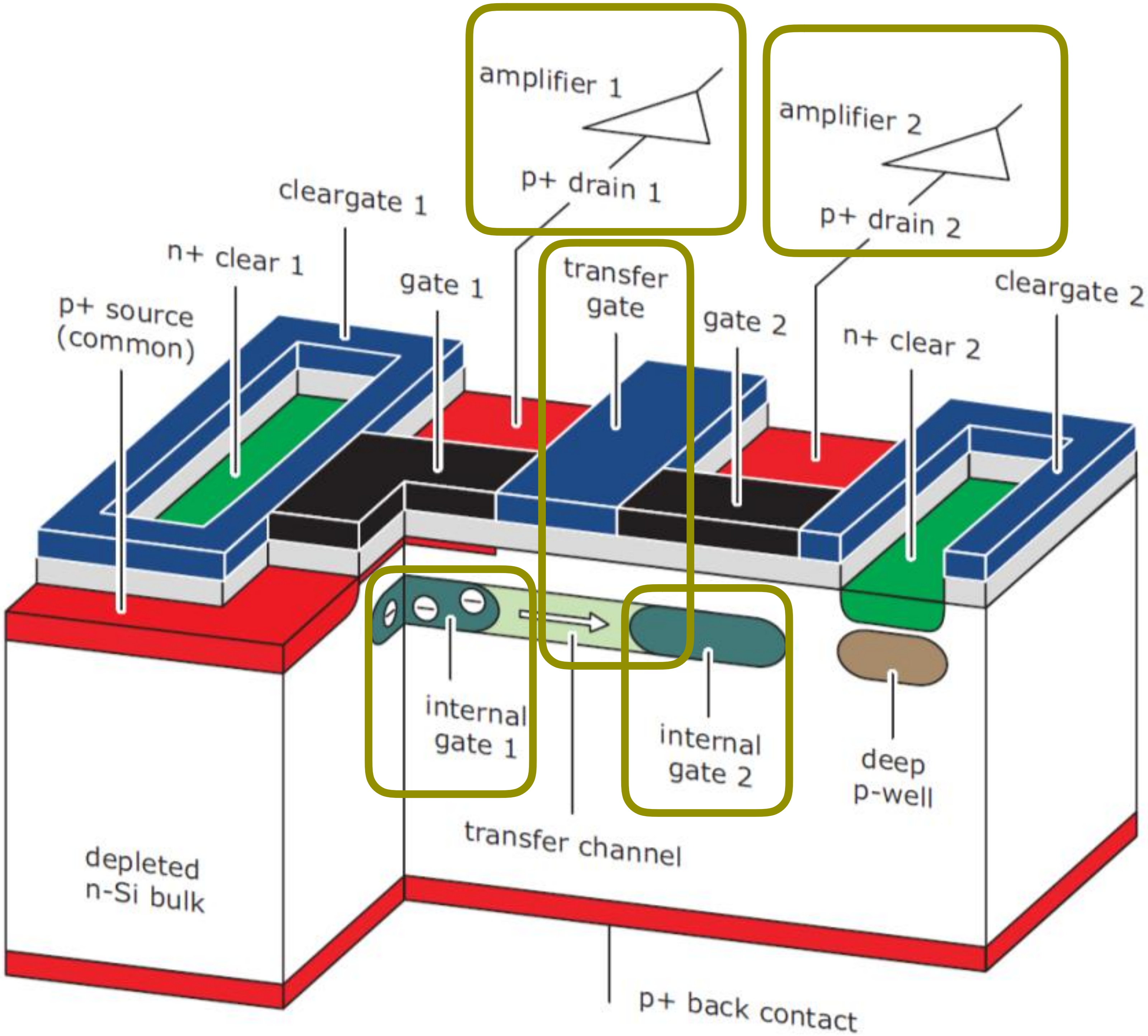
read **1** : noise **σ**

transfer gate open

read N times *effective noise* :

$\boldsymbol{\sigma_{eff} = \sigma/(\sqrt{N})}$

RNDR



EPJ C, 77(12), 279 (2017)

RNDR readout

read **1** : noise **σ**

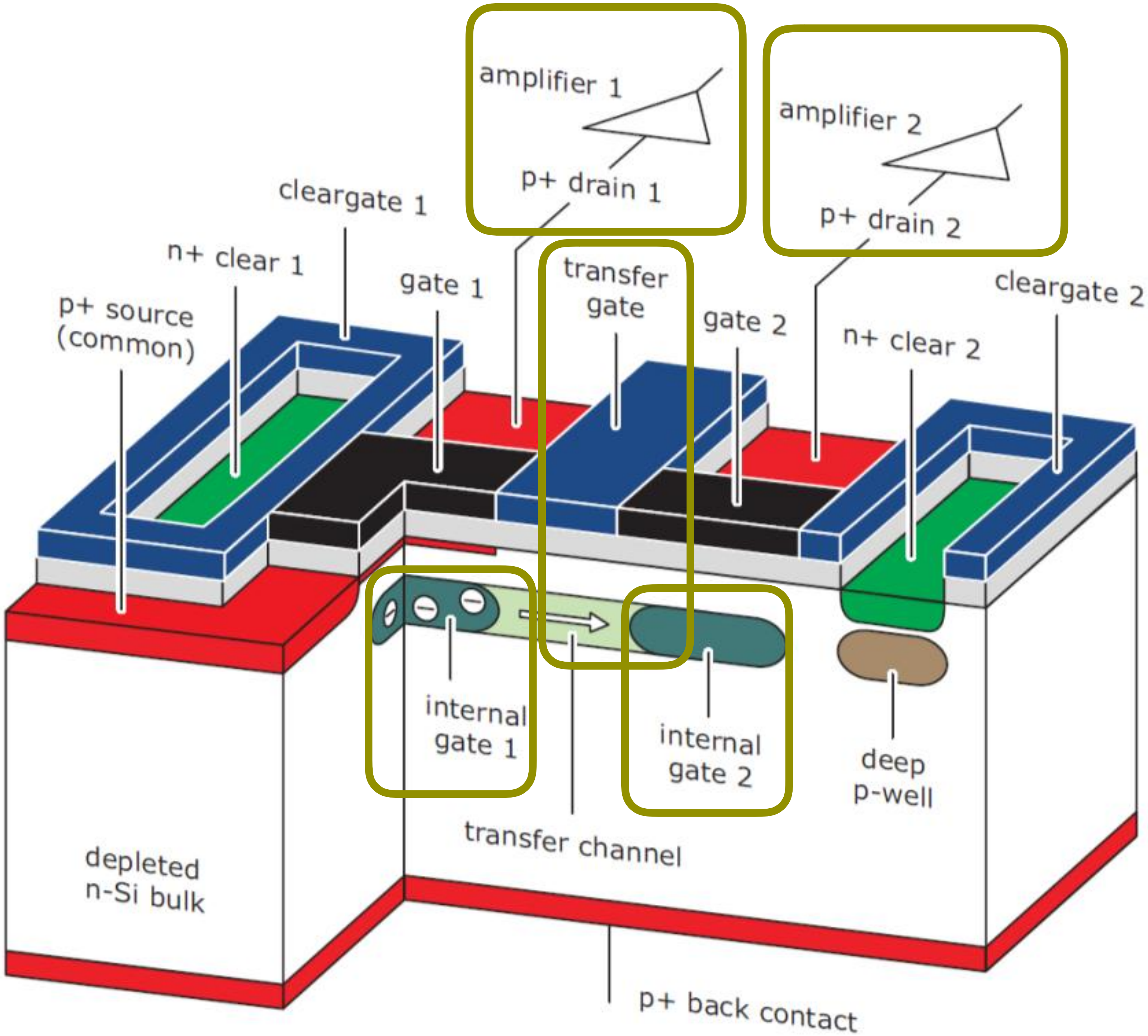
transfer gate open

read **2** : noise **σ**

read N times *effective noise* :

$\boldsymbol{\sigma_{eff} = \sigma/(\sqrt{N})}$

RNDR



EPJ C, 77(12), 279 (2017)

RNDR readout

read **1** : noise **σ**

transfer gate open

read **2** : noise **σ**

: repeat **N** times
independent
measurements

clear charges

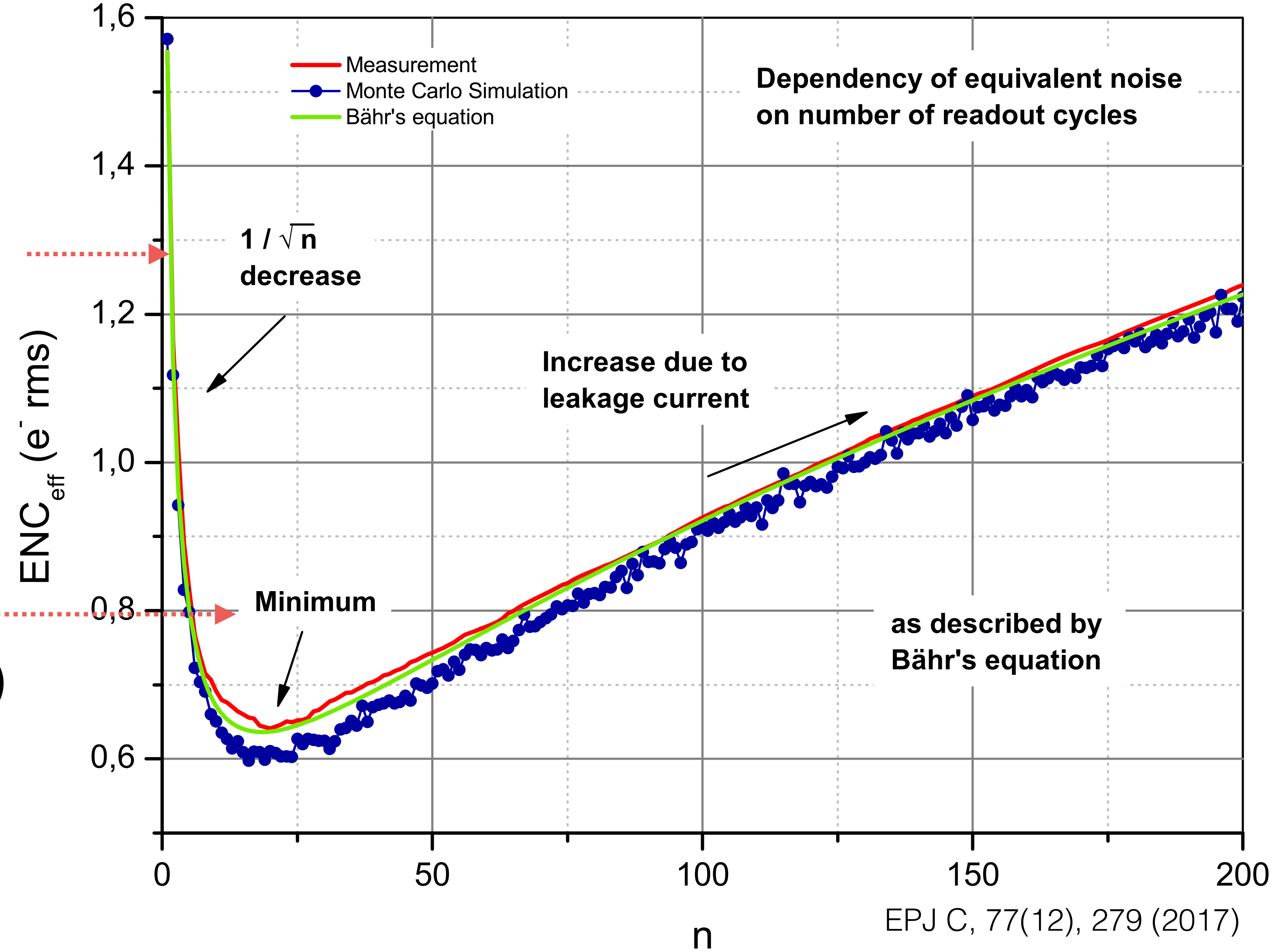
read N times *effective noise* :

$\boldsymbol{\sigma_{eff} = \sigma/(\sqrt{N})}$

DEPFET RNDR single pixel performance

confirmed the 1/√N decrease of σ_{eff}

minimal noise level limited by leakage current at 230 K (-40 °C)



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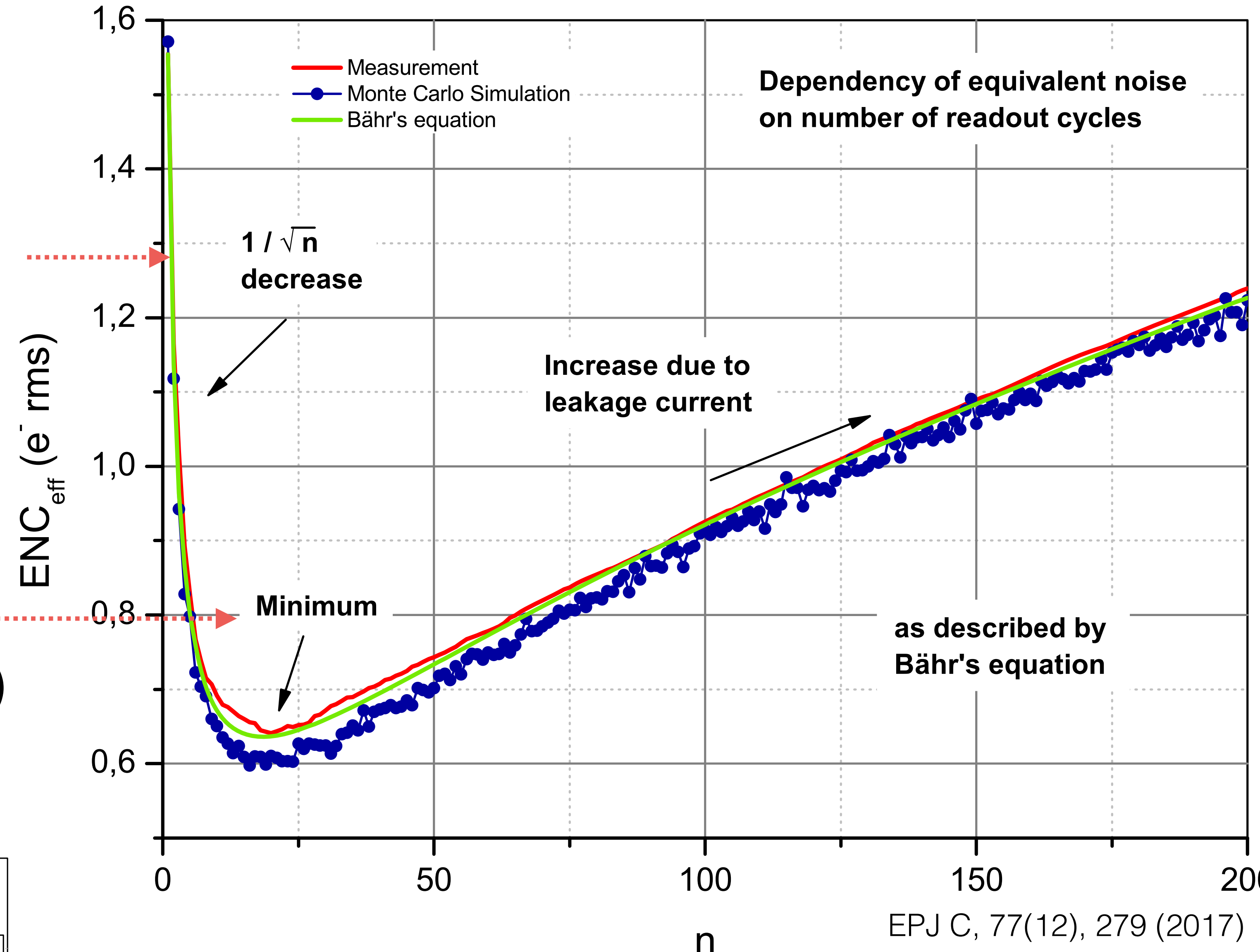

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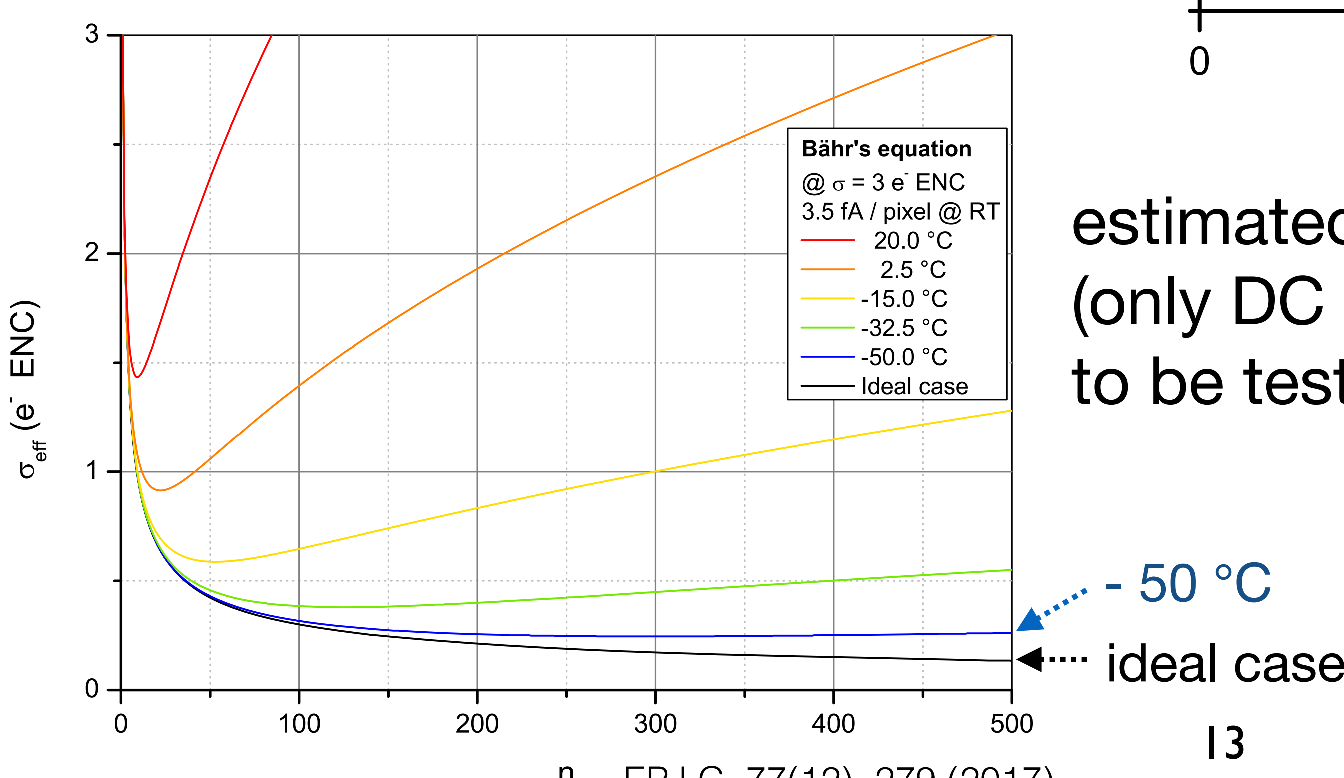

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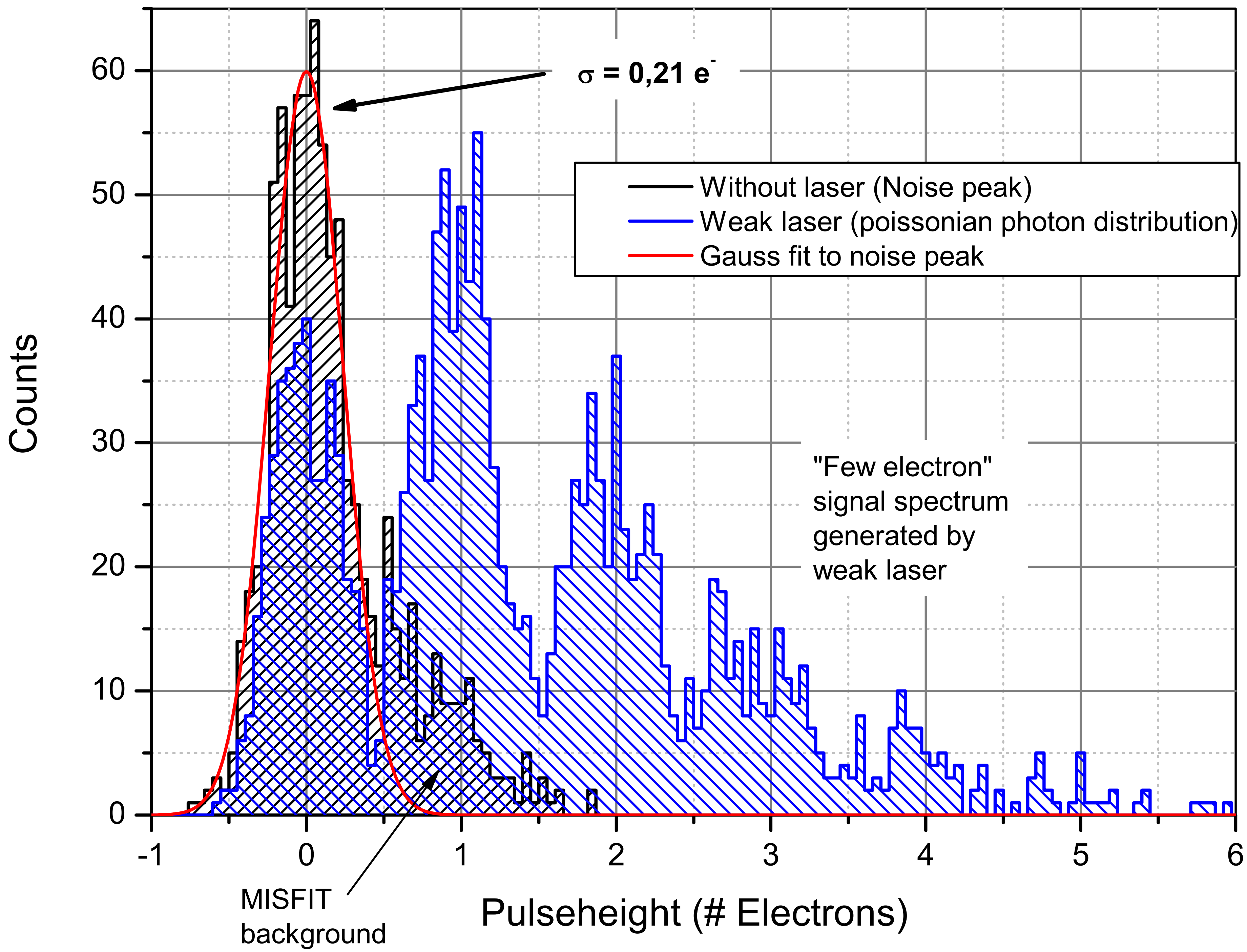
estimated temperature dependence
(only DC from thermal excitation)
to be testified in measurement

DEPFET RNDR single pixel performance



single pixel RNDR DEPFET effective noise :

$0.2\ e^{-}$ RMS at 200 K

capable of distinguish single electron charge

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A comparison with skipper CCD

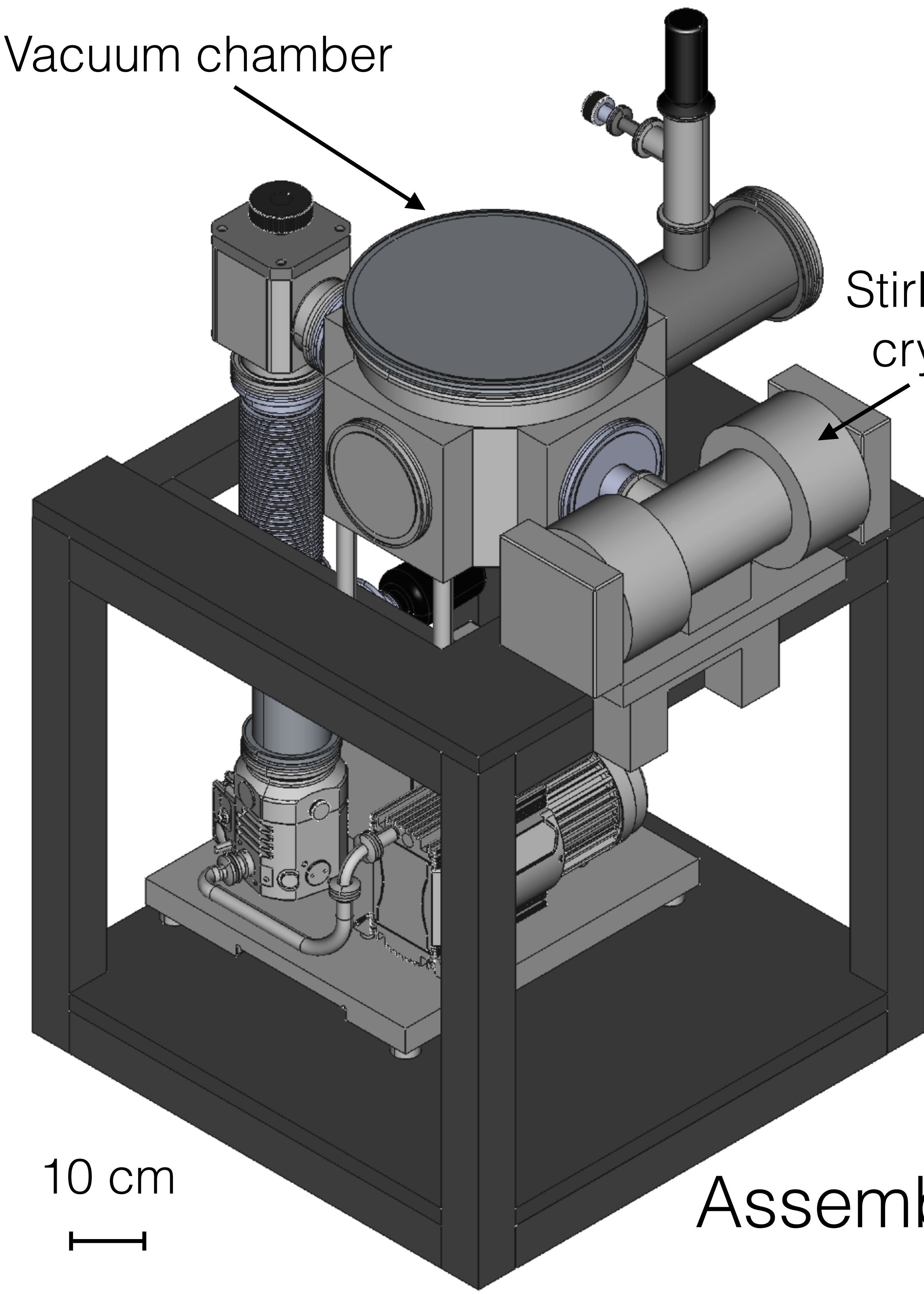
Type	Pixel format [μm]	prototype mass	operating temp	dark current	readout time (1sample)	readout noise (optimal)
skipper CCD	15 x 15 x 200	0.071 g	140 K	< ~1.14 e^-/pix/day	10 μs/pix/ amplifier	0.068 e^-rms/pix
RNDR DEPFET	75 x 75 x 450	0.024 g	$\lesssim$ 200 K	< 1 e^-/pix/day	4 μs/ 64 pix	0.2 e^-rms/pix

similar concepts of non-destructive readout, compatible performance;

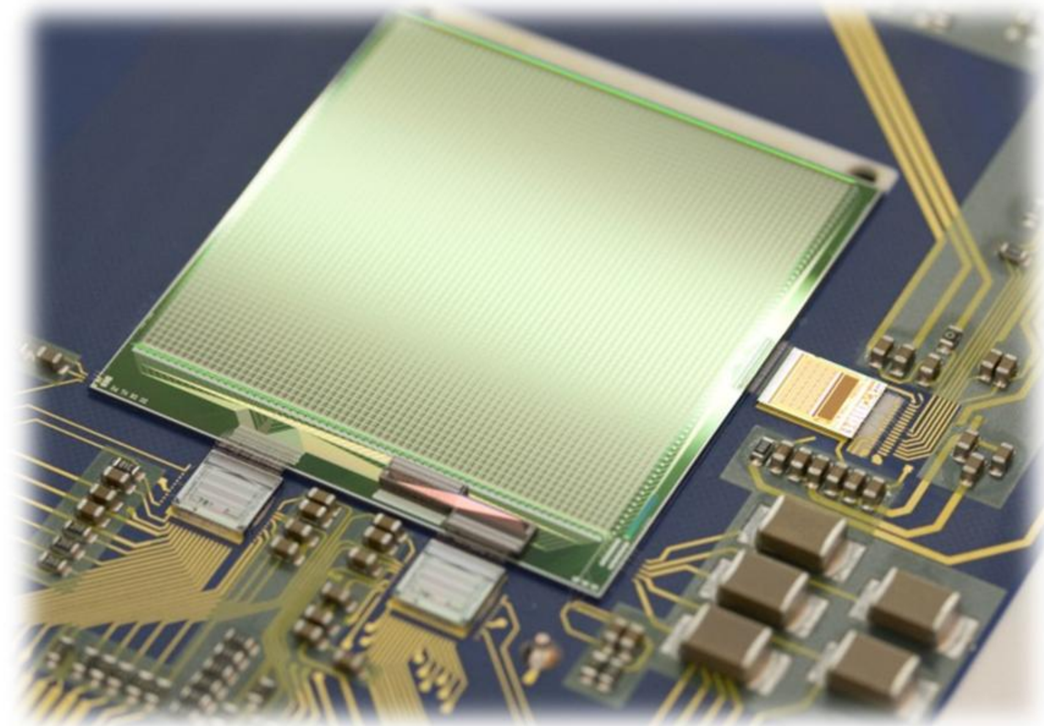
different architecture, different systematics;

-> good complementary from experimental point of view

DANAE prototype test setup



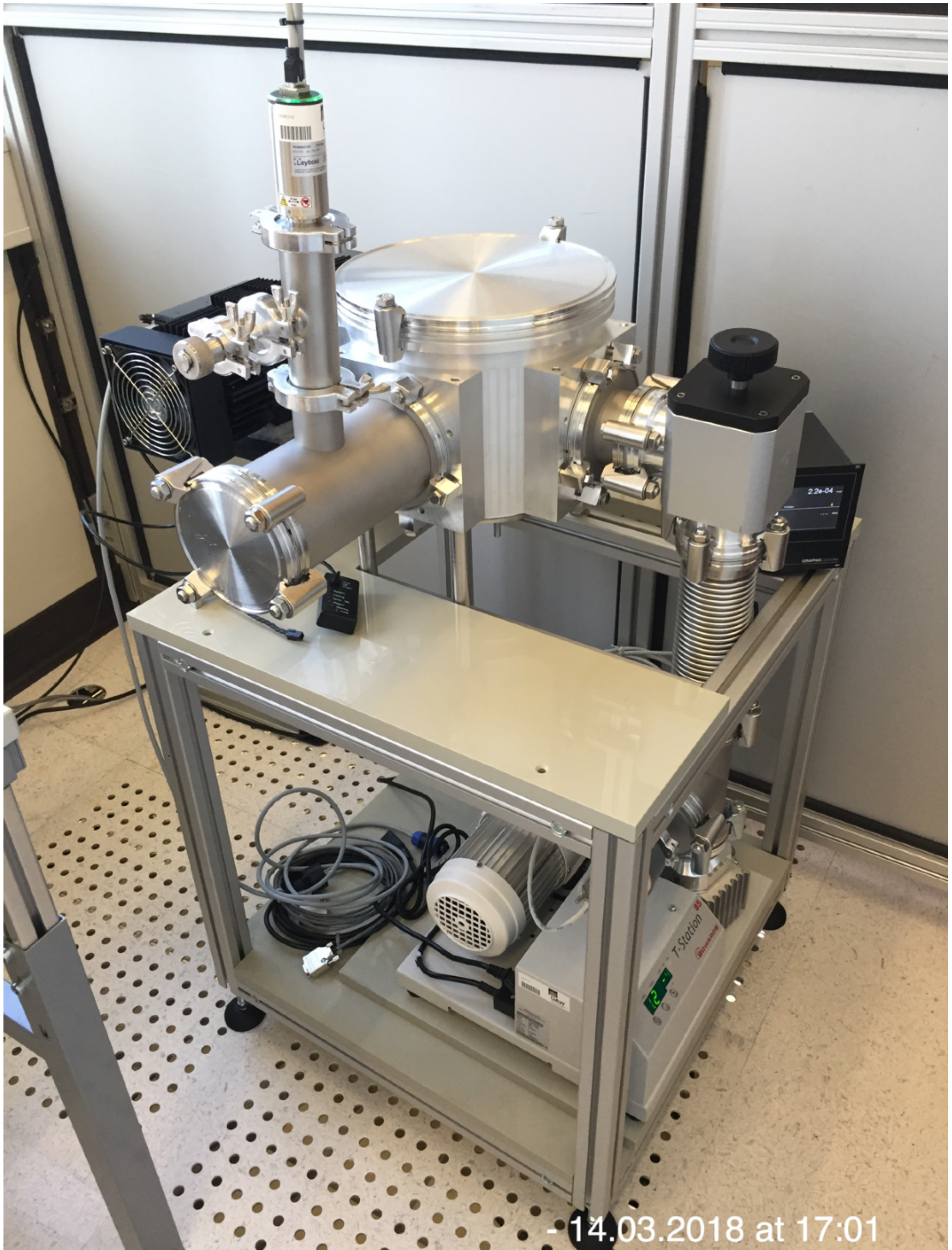
Assembly at HLL

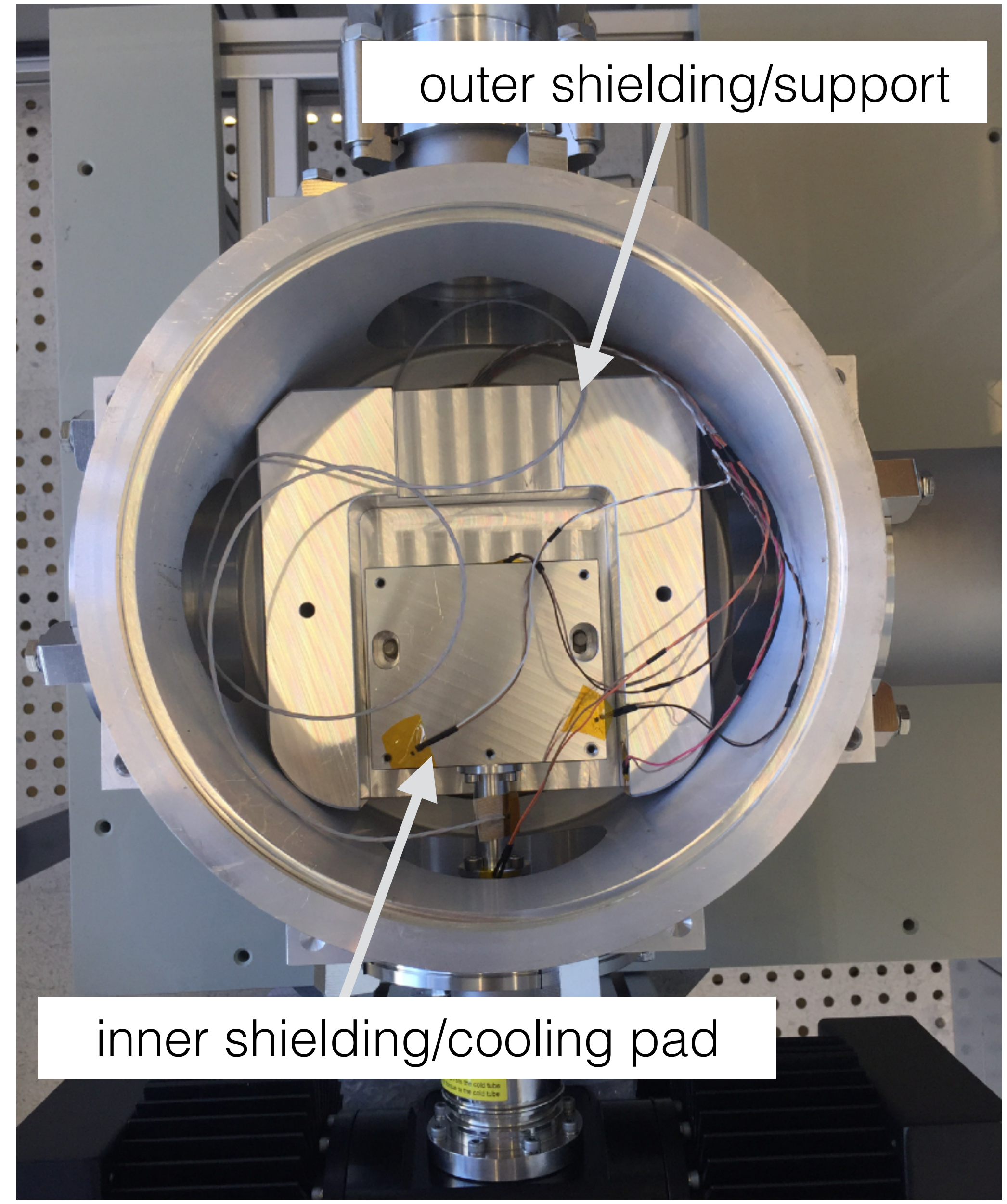


Detector prototype at HLL-MPG
courtesy of J. Treis

proto-type :
75 um x 75 um x 450 um single pixel,
64 x 64 matrix
sensitive volume **0.024 g**

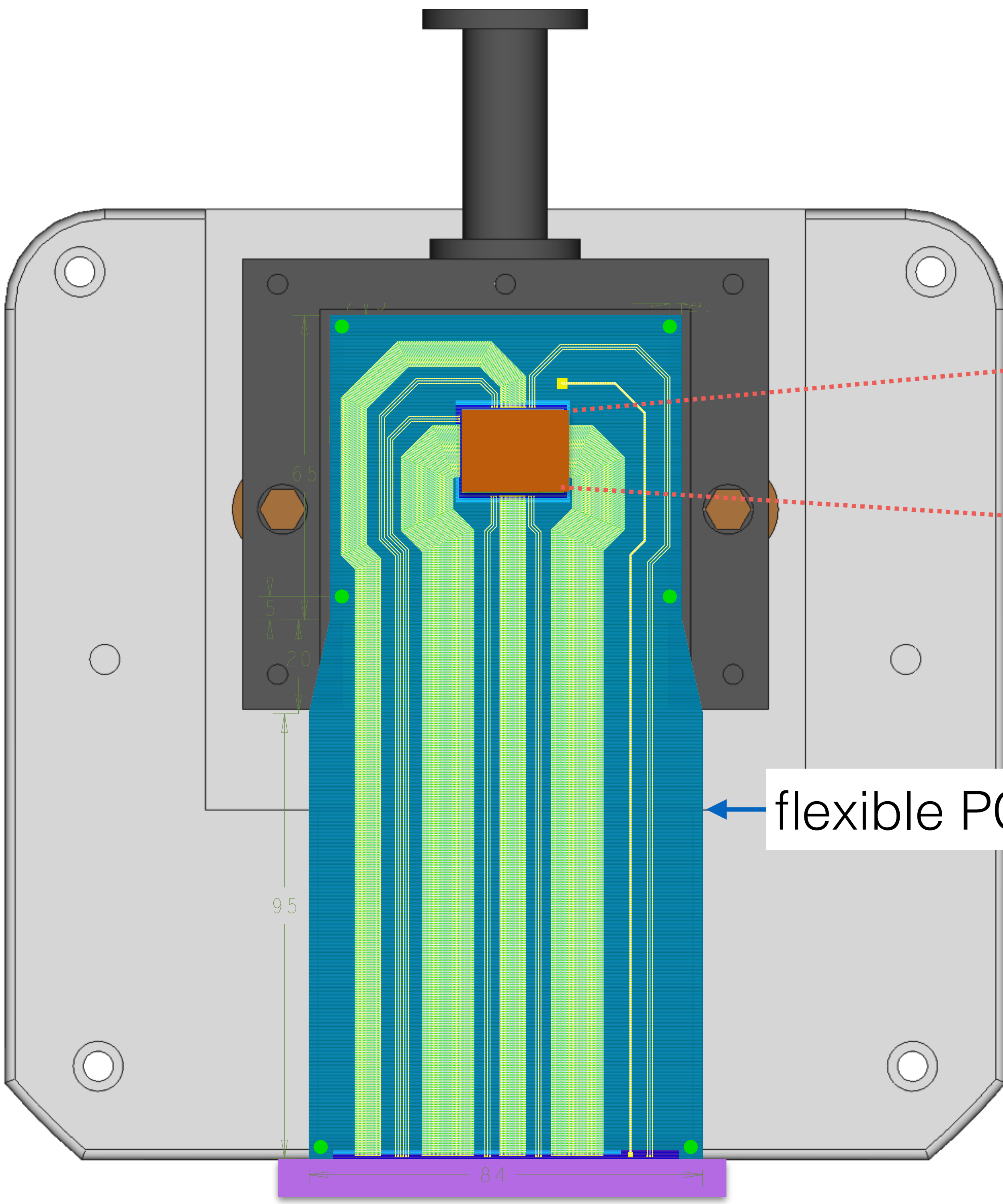
Setup at HLL





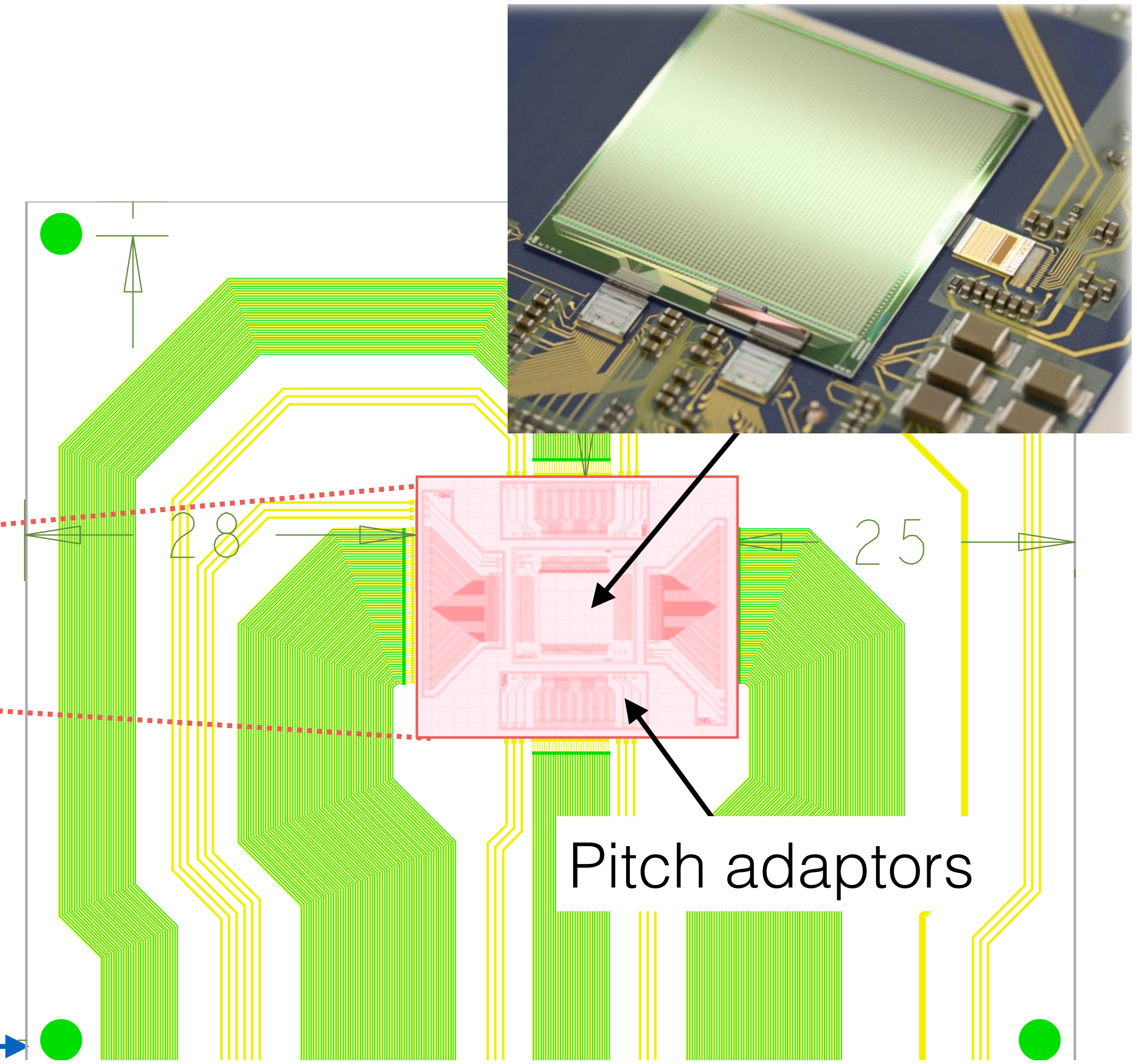
Vacuum and cooling test in March 2018
cooling pad reached 150 K

Detector control and readout electronics



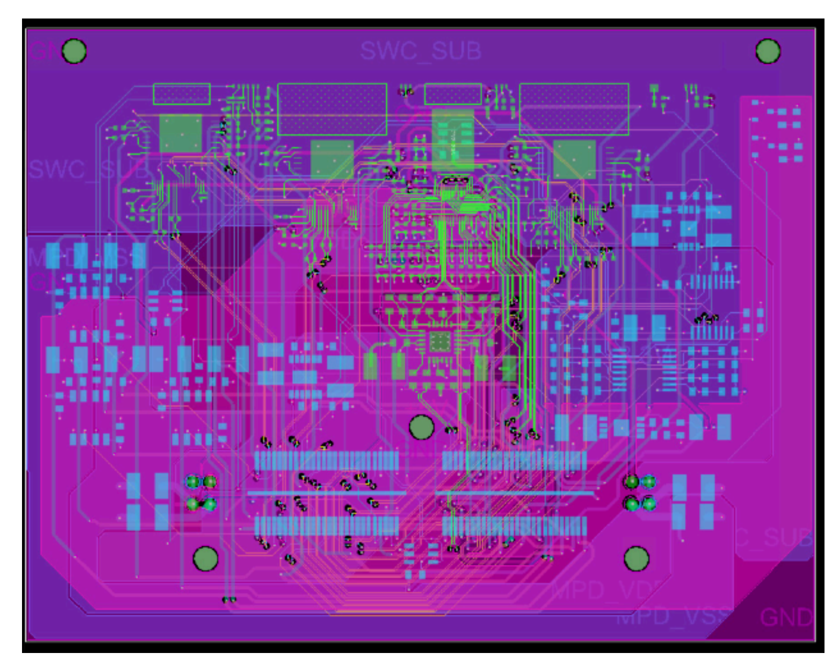
flexible PCB

detector matrix



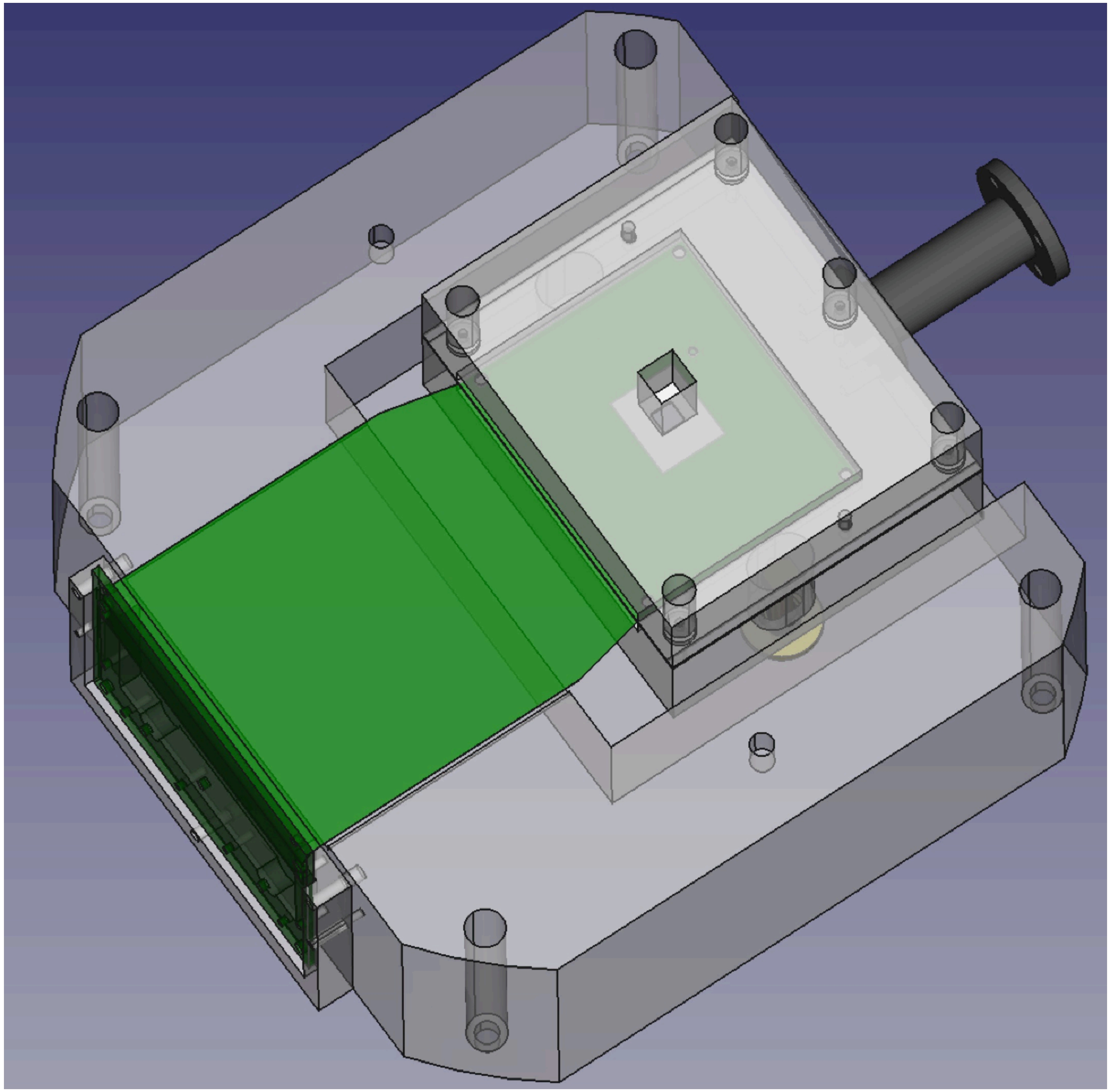
Pitch adaptors

Readout board
(consists of gate-control
and readout ASICs)



J. Treis
HLL

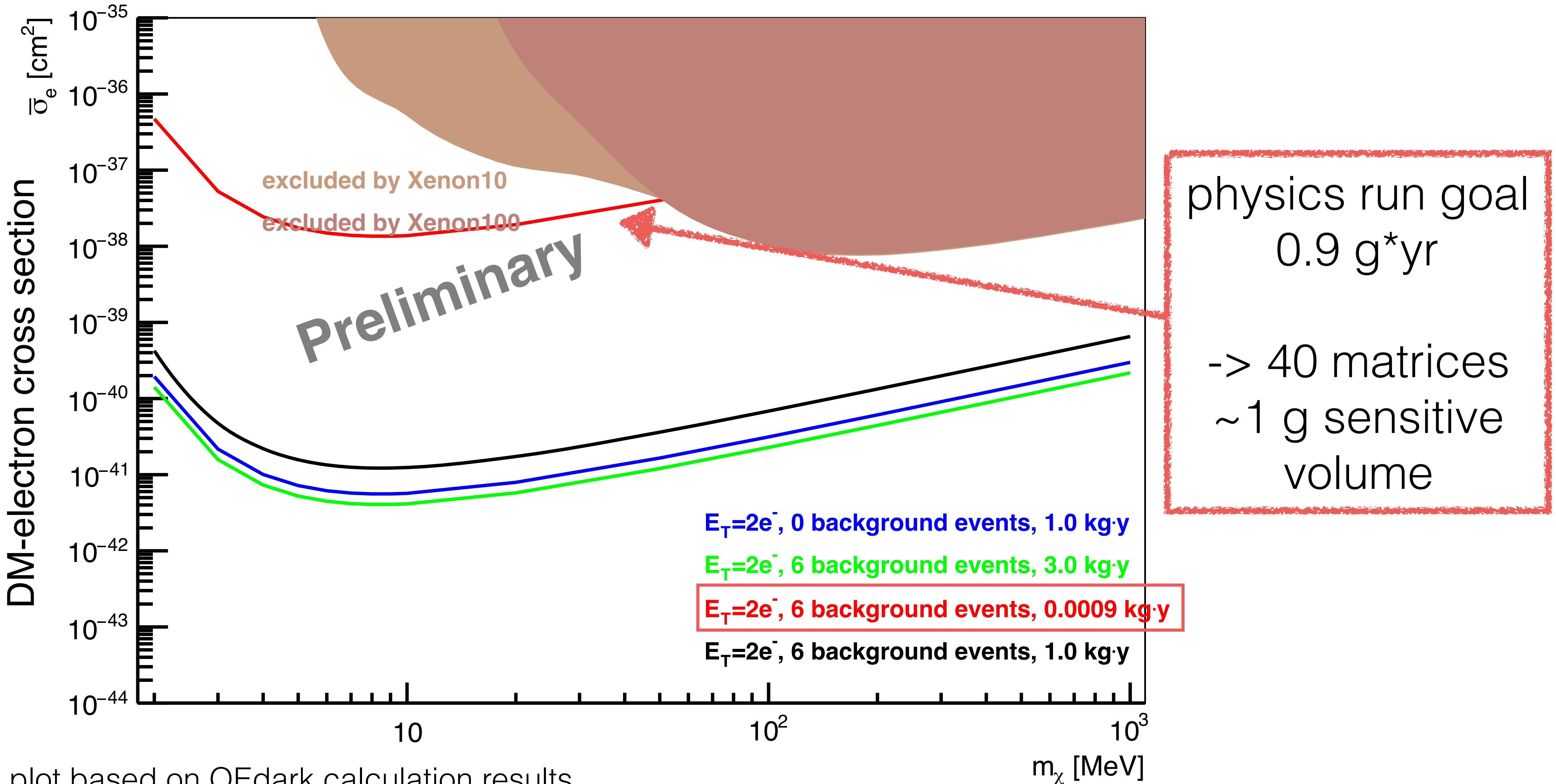
Image of the detector assembly



To be assembled in July-August 2018

Physics run perspective

- Expect preliminary results from the prototype setup (0.024 g sensitive volume) in late 2018
- physics run with significant result requires more matrices



plot based on QEdark calculation results

JHEP05(2016)046

Summary

- sub e^- ENC low noise semiconductor detector capable of detecting the energy deposit from sub-GeV DM-electron recoil;
- DANAE prototype for test-of-principle measurement with 64 x 64 pixel matrix in preparation;
- one of the first generation experiments using non-destructive repetitive readout method.

DANAE (DANAË)

Direct dArk matter search using DEPFET with repetitive-Non-destructive-readout Application Experiment

OeAW funding for detector technology

"Danae" by G. Klimt

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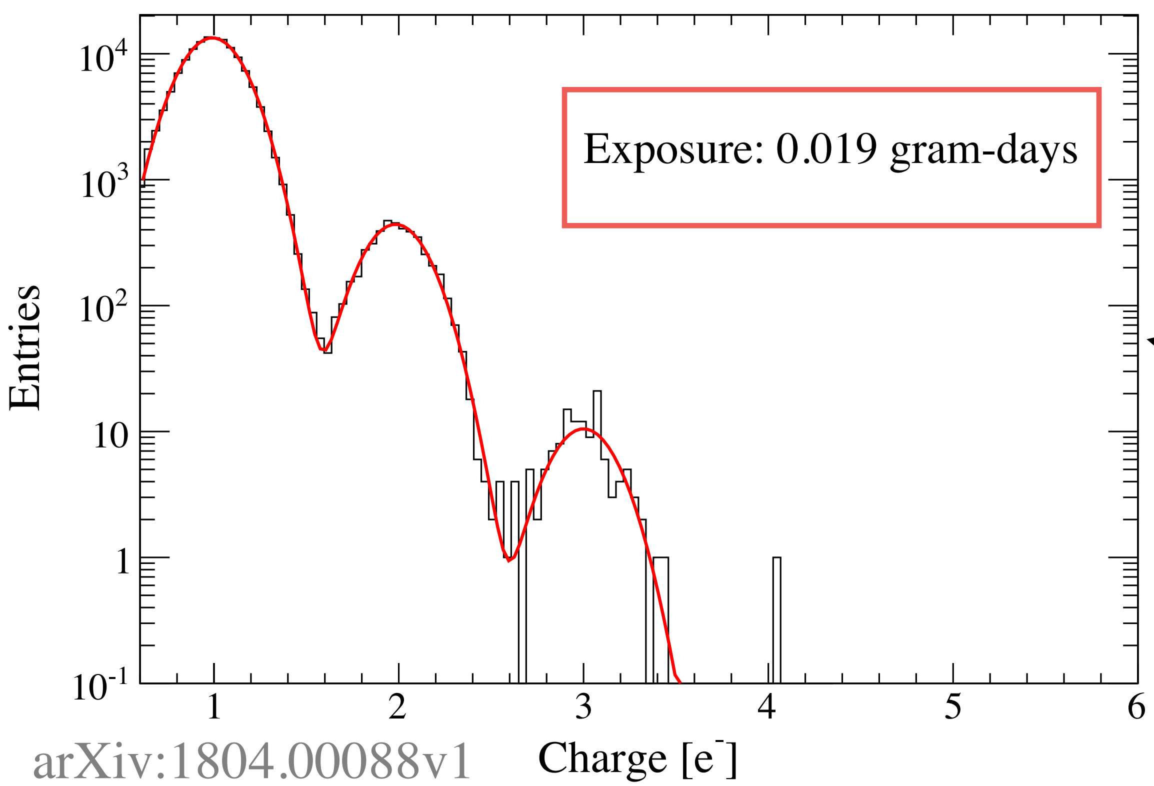
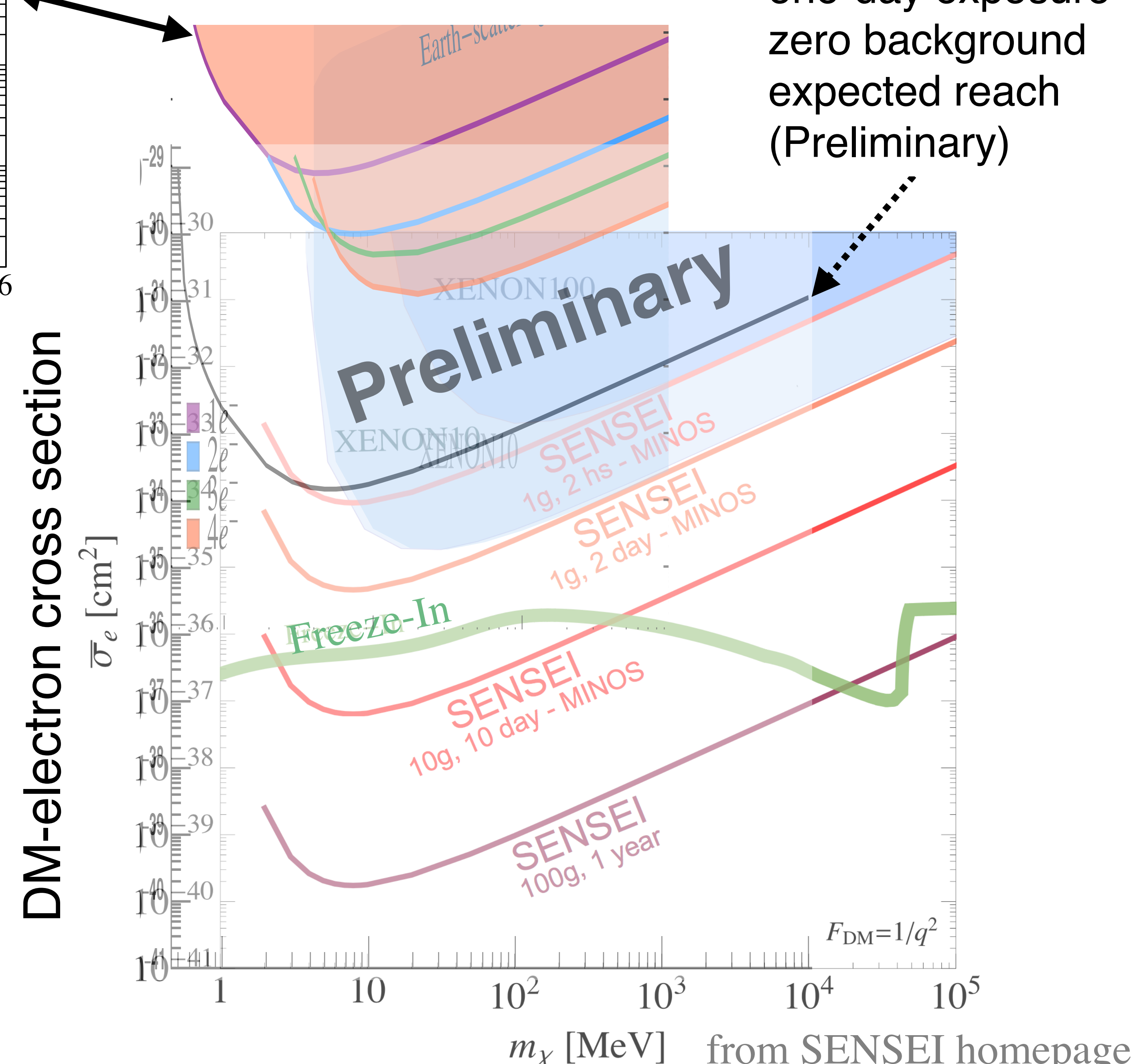
Expected 1day exposure compared to SENSEI

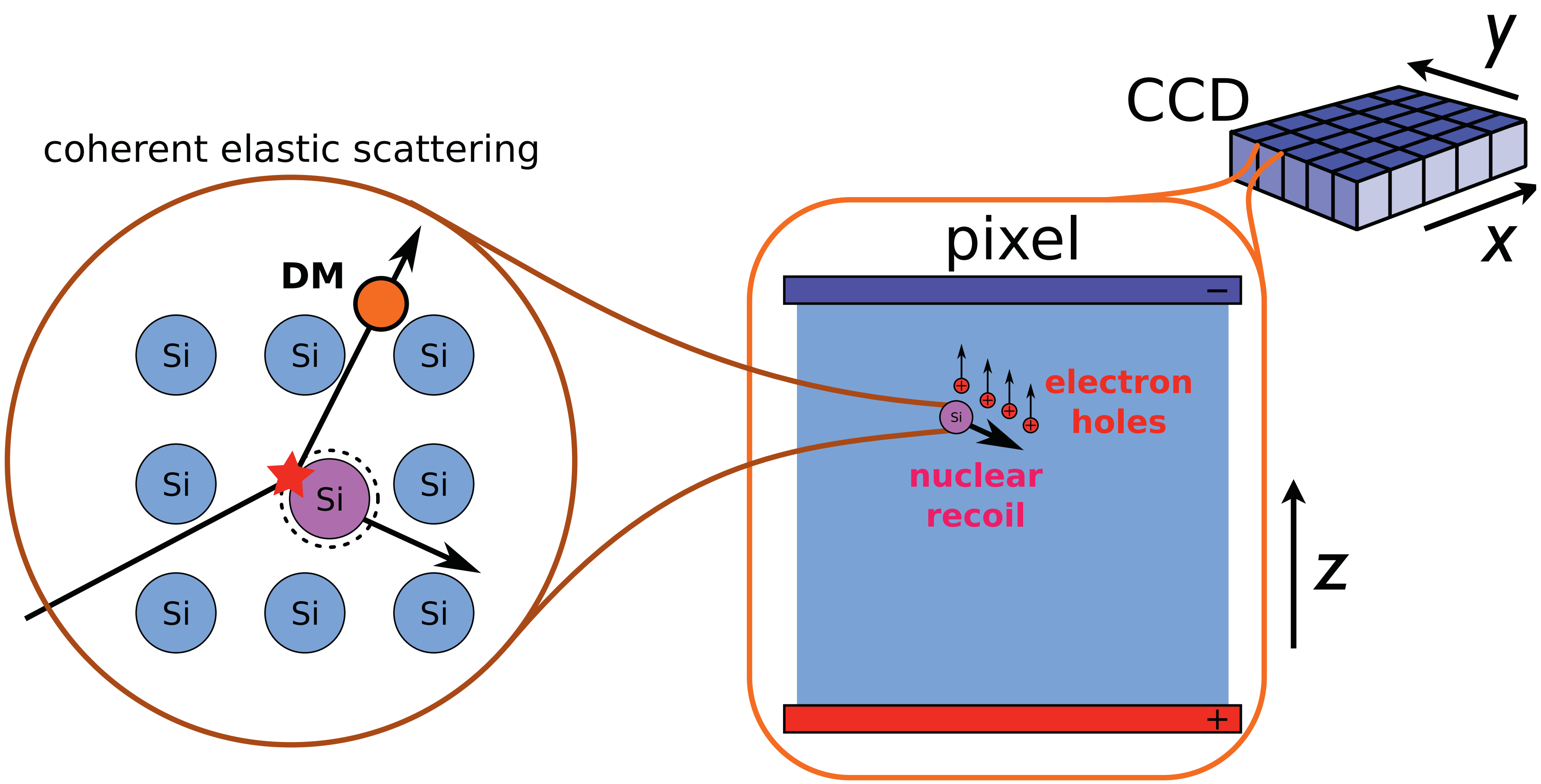




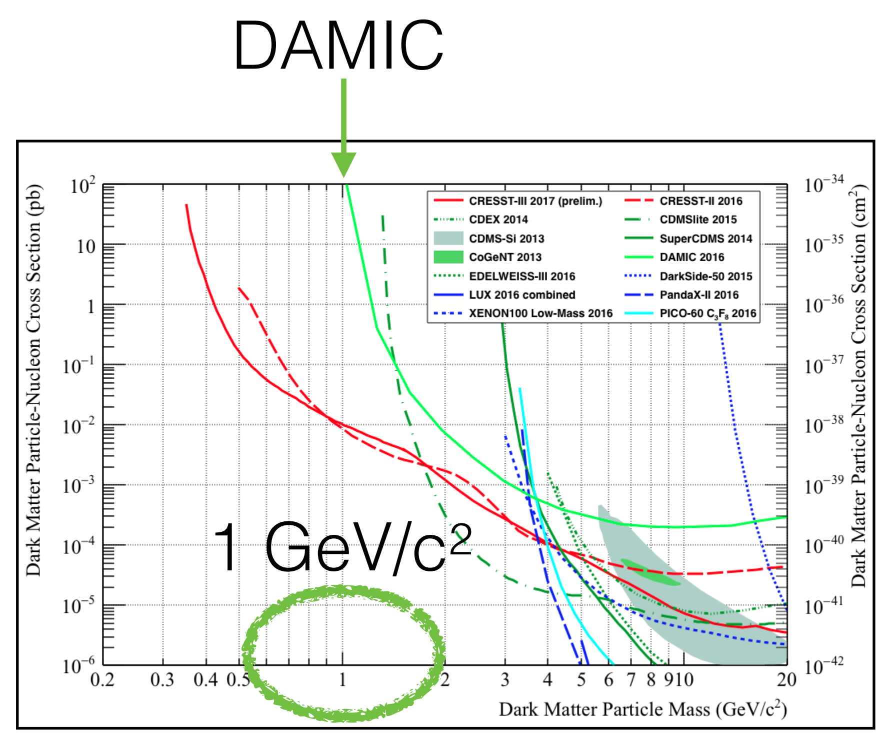
Application of Silicon detector

DAMIC

nucleus recoil   CCD, with physics results



Physics Procedia 61 (2015) 21 – 33

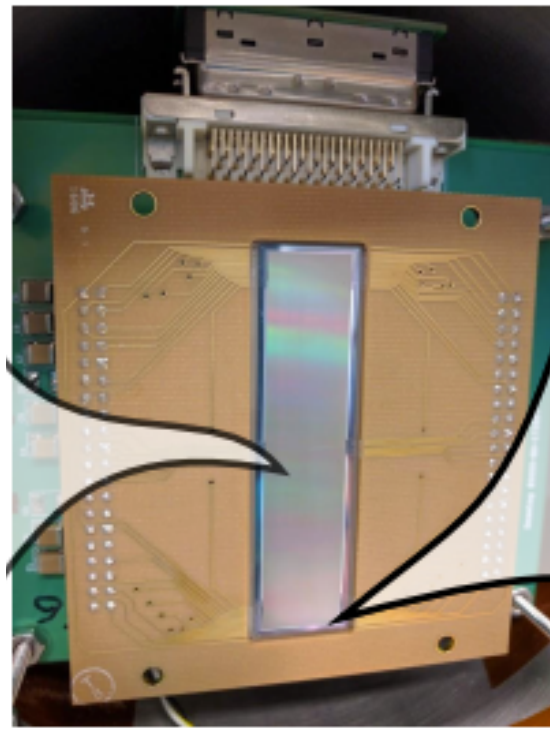


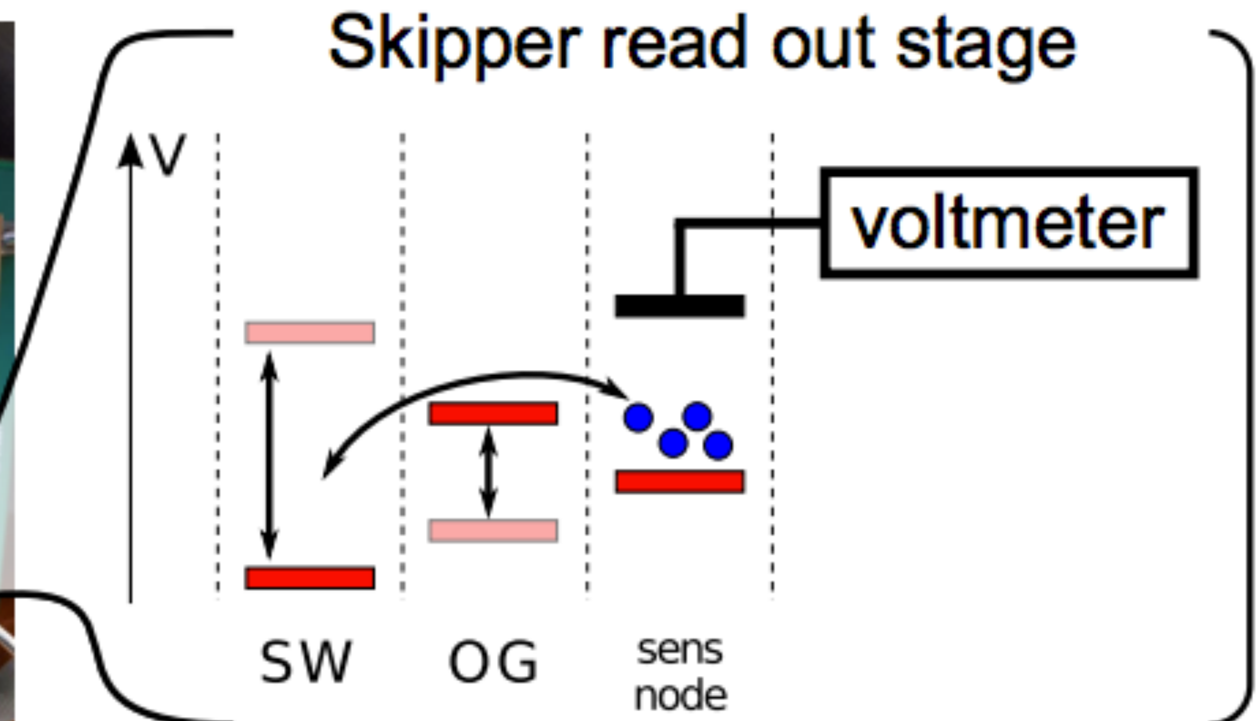
Readout noise determines threshold of ~ 11 e⁻ (or ~ 40 eV)

For O(MeV) DM-electron scattering, required threshold : O(e⁻)
Sub-electron noise level necessary

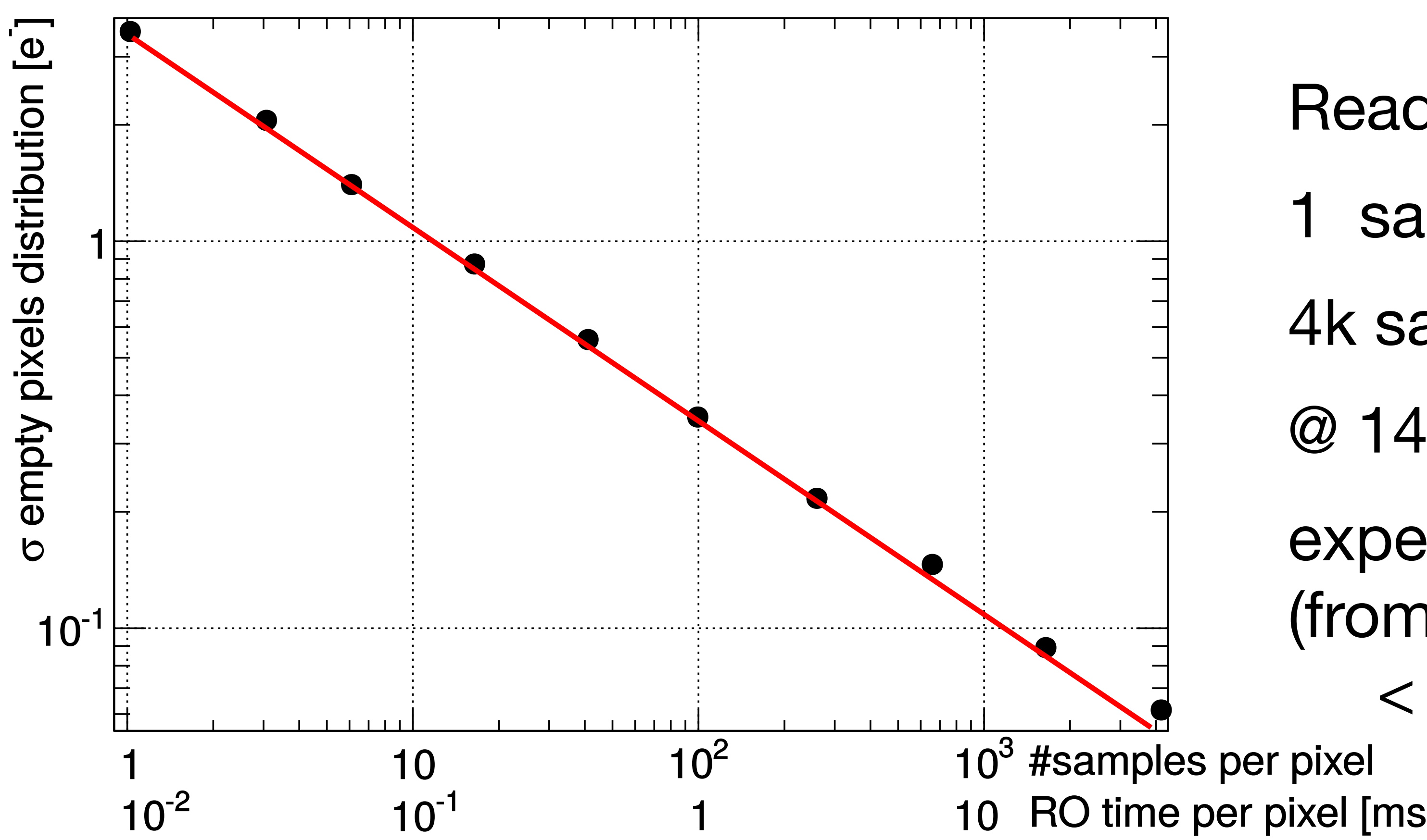
Skipper CCD for SENSEI

DAMIC CCD with **repetitive readout**





from SENSEI homepage



PRL 119(1) 131802 (2017)

Readout noise :

1 sample : 3.55 e^- rms

4k samples : 0.068 e^- rms

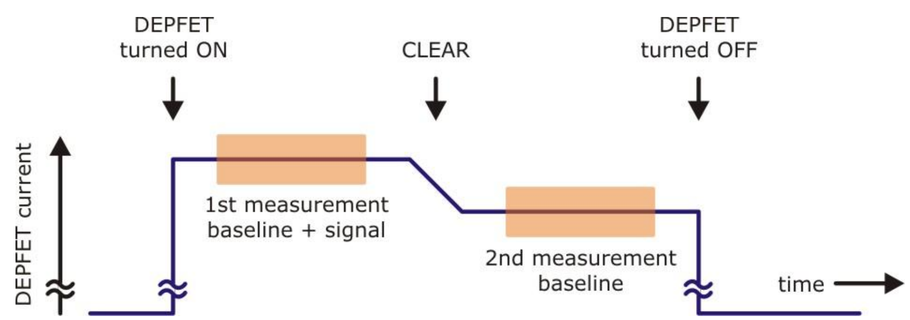
@ 140 K

expected dark current (from DAMIC CCD) :
$< 10^{-3}$ e^-/pix/day

DEPFET CDS circle

Detector Structures – Matrix Devices

- **readout sequence**



Correlated double sampling:

1st measurement: signal + baseline

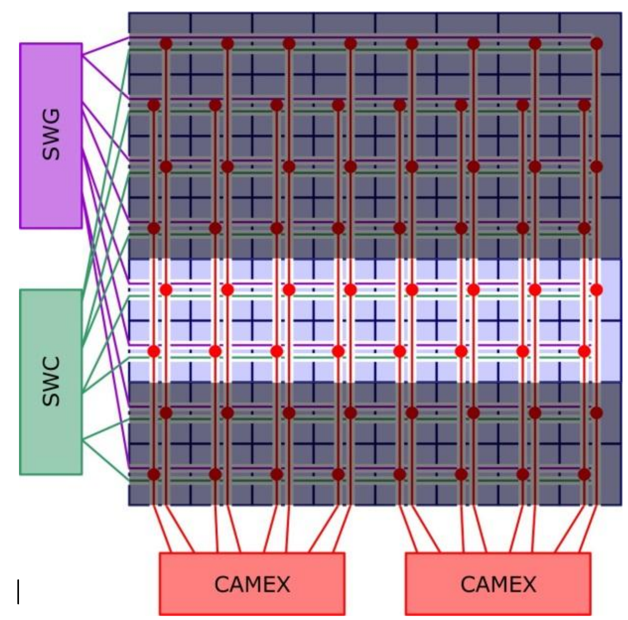
clear: removal of signal charges

2nd measurement: baseline

difference = signal

complete clear is mandatory!

- **matrix operation**



vertical signal lines

1 active row, other pixels integrating

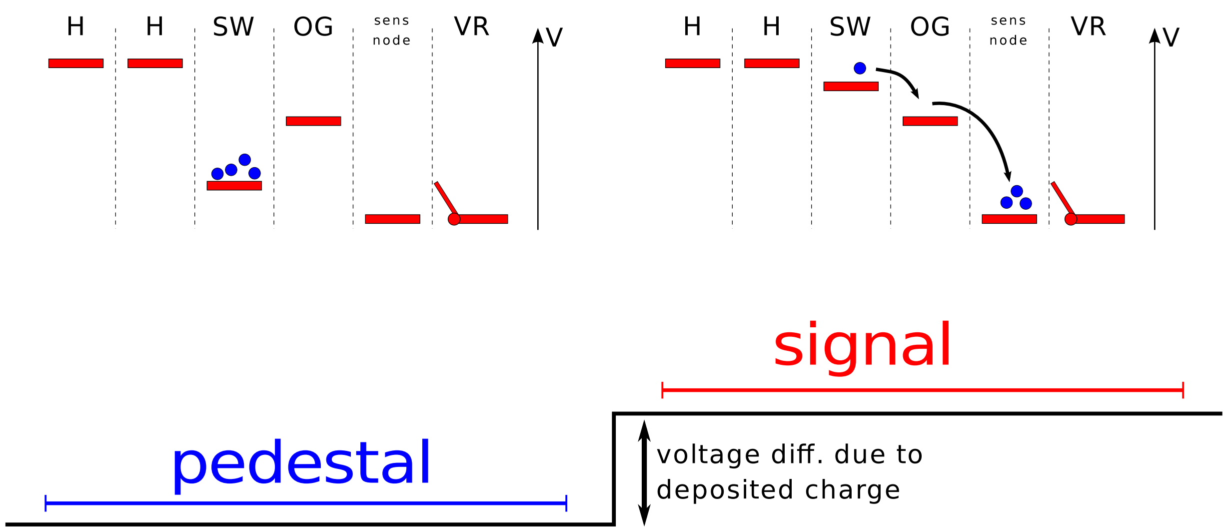
- **option to speed up (1)**

readout parallelisation

2 x readout channels, 2 active rows

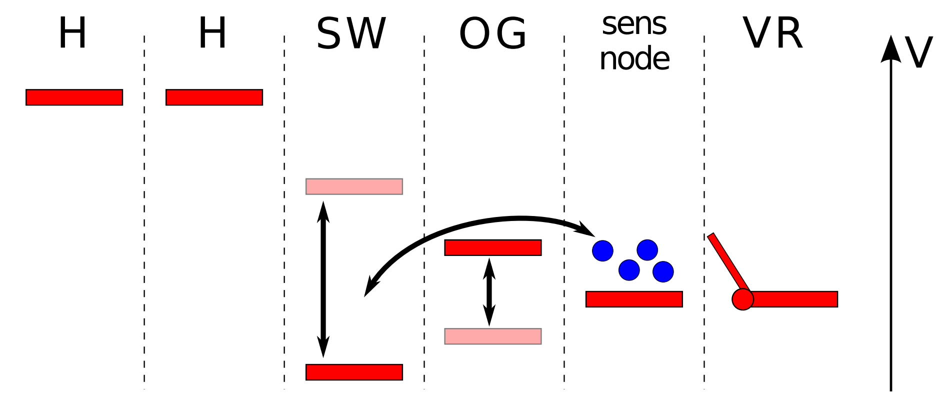
CCD (skipper) readout

CCD: readout



Lowering the noise: Skipper CCD

- **Main difference:** the Skipper CCD allows multiple sampling of the same pixel without corrupting the charge packet.
- The final pixel value is the average of the samples
  Pixel value $= \frac{1}{N}\Sigma_i^N$ **(pixel sample)**$_i$



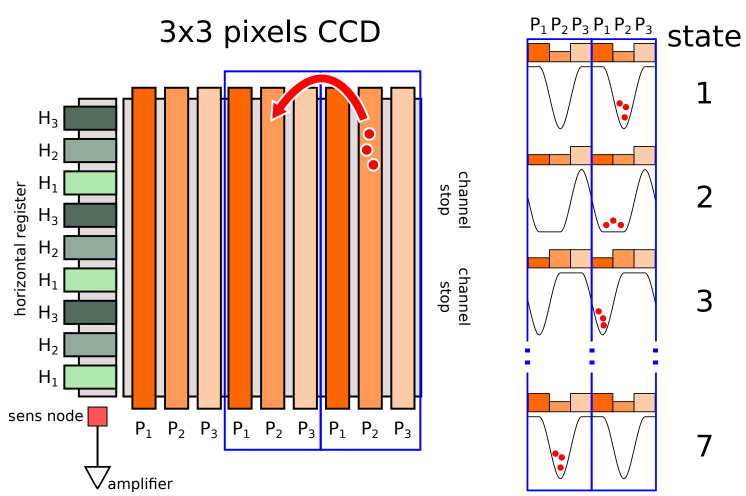
SW : summing-well gate

OG : output gate

RG : reset gate

VR : V_ref

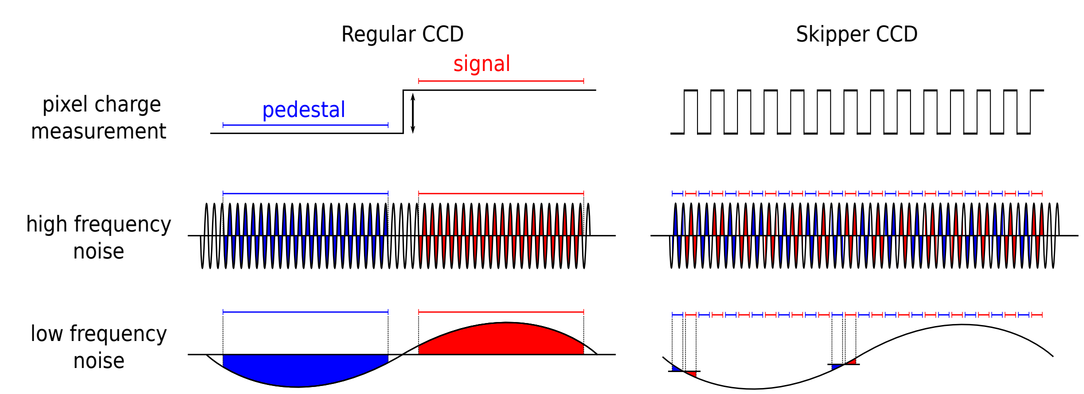
CCD: readout



capacitance of the system is set by the SN: C=0.05pF$\rightarrow$ 3μV/e

Lowering the noise: Skipper CCD

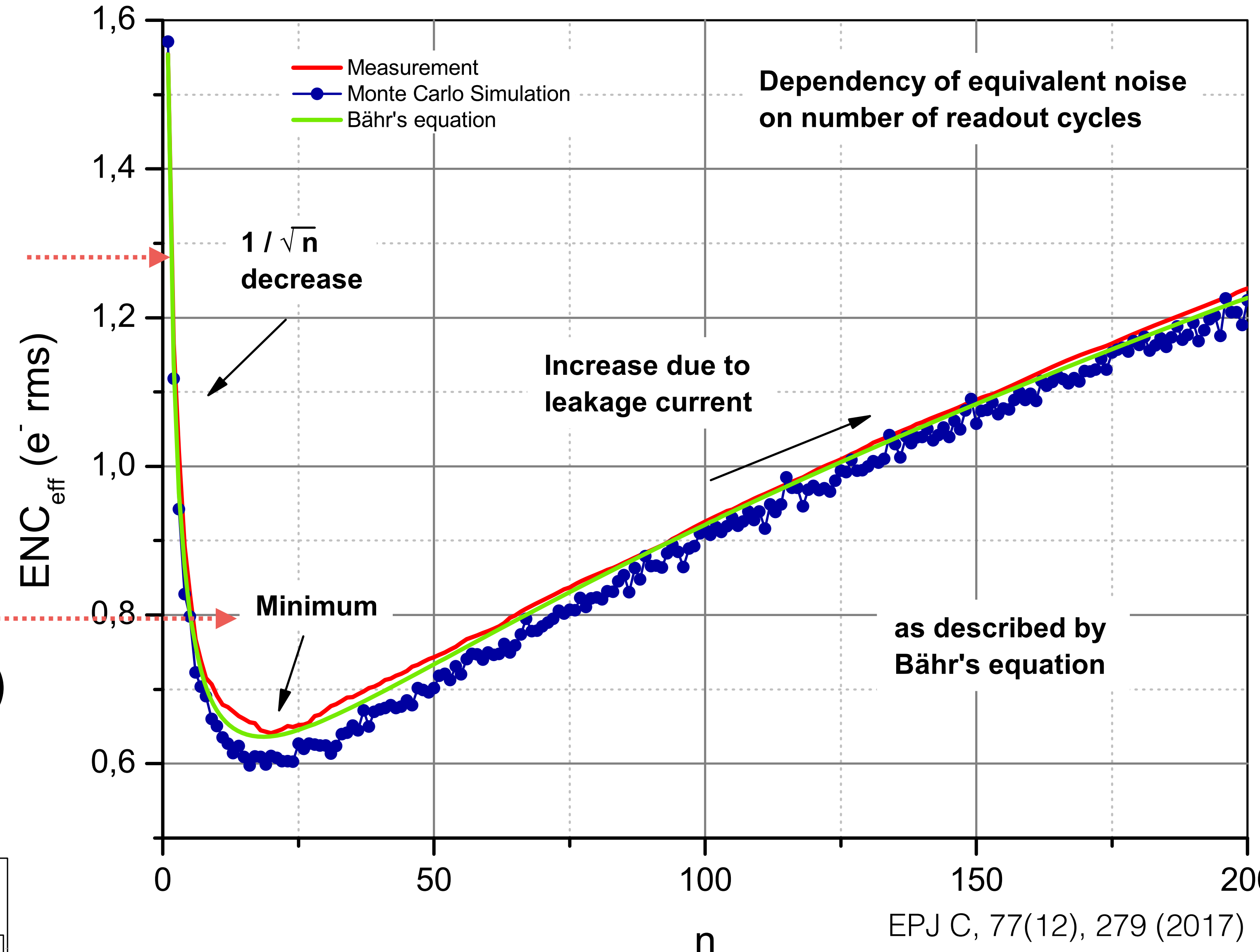
- **Main difference:** the Skipper CCD allows multiple sampling of the same pixel without corrupting the charge packet.
- The final pixel value is the average of the samples
  Pixel value $= \frac{1}{N}\Sigma_i^N$ **(pixel sample)**$_i$



Javier Tiffenberg

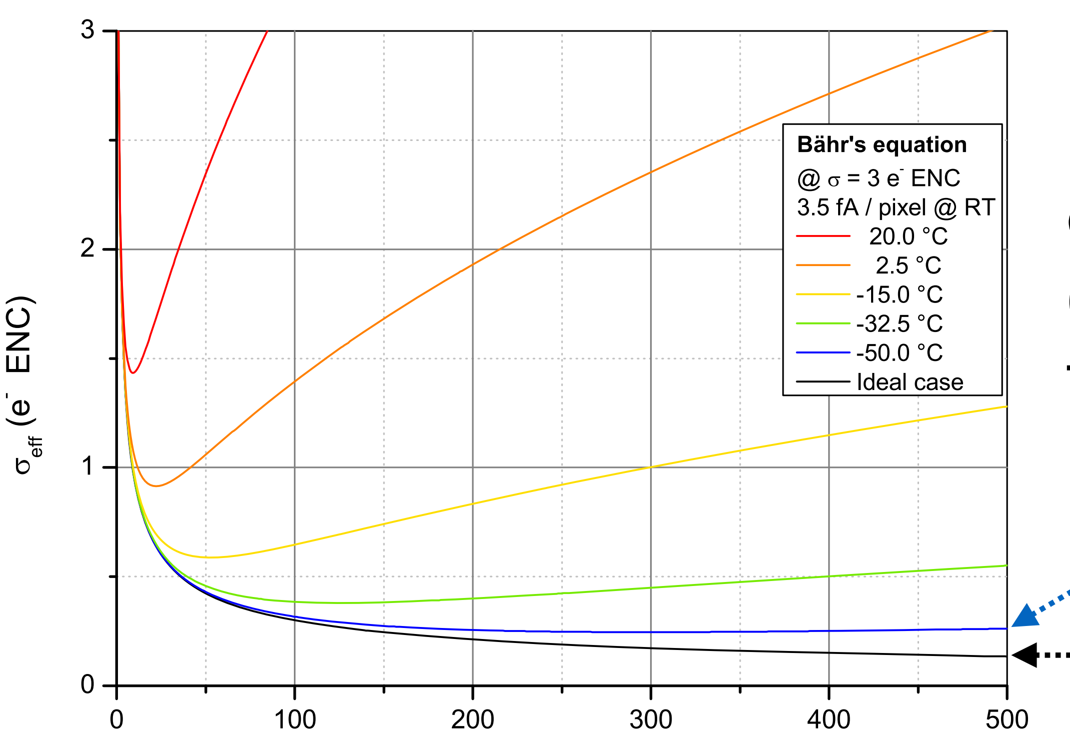
DEPFET RNDR single pixel performance

confirmed the 1/√N decrease of σ_{eff}



EPJ C, 77(12), 279 (2017)

minimal noise level limited by
leakage current at 230 K (-40 °C)



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- 50 °C

ideal case

estimated temperature dependence
(only DC from thermal excitation)
to be testified in measurement

new architecture with “blind-gate”

possibility of reducing leakage
current during readout